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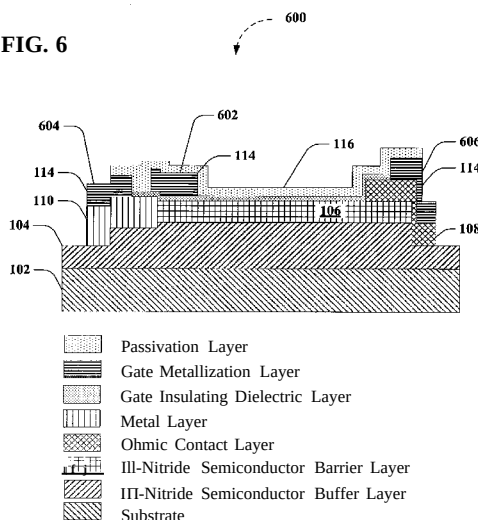
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FIG. 6



(57) Abstract: Structures, devices and methods are provided for creating heterojunction AlGaIn/GaN metal two-dimensional electron gas (2DEG) tunnel-junction field-effect transistors (TJ-FET). In one aspect, metal-2DEG Schottky tunnel junctions can be employed in group III-Nitride field-effect devices that enable normally-off operation, large breakdown voltage, low leakage current, and high on/off current ratio. As a further advantage, AlGaIn/GaN metal-2DEG TJ-FETs are disclosed that can be fabricated in a lateral configuration and/or a vertical configuration. Further non-limiting embodiments are provided that illustrate the advantages and flexibility of the disclosed structures.

NORMALLY-OFF III-NITRIDE METAL-2DEG TUNNEL JUNCTION FIELD-EFFECT TRANSISTORS

5 FIELD OF THE INVENTION

This application claims priority to U.S. Provisional Patent Application Serial No. 61/344,356, filed on July 06, 2010, and entitled NORMALLY-OFF III-NITRIDE SCHOTTKY-SOURCE TUNNEL HETEROSTRUCTURE FIELD-EFFECT TRANSISTORS AND THE METHOD OF MAKING THE SAME, the entirety of
10 which is hereby incorporated by reference.

FIELD OF THE INVENTION

The subject disclosure is directed to field effect transistors and, more specifically, to structures, devices, and methods for creating normally-off Ill-nitride
15 Metal two-dimensional electron gas (2DEG) tunnel junction field-effect transistors.

BACKGROUND OF THE INVENTION

High Electron Mobility Transistors (HEMTs), also called heterostructure field-effect transistors (HFETs) or modulation-doped field-effect transistors
20 (MODFETs), are field effect transistors typically incorporating a junction between two materials with different band gaps, *e.g.*, a heterojunction, as the channel instead of a doped region. HEMTs use high mobility electrons generated by a heterojunction comprised of a highly-doped wider-bandgap n-type donor-supply layer, or unintentionally doped Aluminum-Gallium-Nitride (AlGaN), for example, and a non-
25 doped narrower-bandgap layer with little or no intentional dopants, *e.g.*, Gallium-Nitride (GaN).

For example, electrons generated in an n-type donor-supply layer can drop into the non-doped narrower-bandgap channel at the heterojunction to form a thin depleted n-type donor-supply sub-layer and narrower-bandgap channel, due to the
30 heterojunction created by different band-gap materials forming an electron potential well in the conduction band on the non-doped side of the heterojunction. In the framework of AlGaN/GaN heterostructures, there is often no dopant required in the AlGaN layer due to the strong spontaneous and piezoelectric polarization effect in

such systems. For example, electrons from surface donors can be swept into the GaN channel by the intrinsic polarization induced electric field. In this instance, the electrons can move quickly without colliding with any impurities, due to the unintentionally doped (*e.g.*, not intentionally doped) layer's relative lack of impurities or dopants, from which the electrons cannot escape. The net result of such a heterojunction is to create a very thin layer of highly mobile conducting electrons with very high concentration or density, giving the channel very low resistivity. This layer is known as a two-dimensional electron gas (2DEG). As can be expected in field-effect transistors (FET), voltage applied to the gate alters the conductivity of this layer to form transistor structures.

One kind of high-electron mobility transistor (HEMT) including Gallium Nitride is known as an Aluminum Gallium Nitride/Gallium Nitride (AlGa_N/Ga_N) HEMT, or an AlGa_N/Ga_N HEMT. Typically, AlGa_N/Ga_N HEMTs can be fabricated by growing crystalline films of Ga_N, AlGa_N, *etc.* on a substrate (*e.g.*, sapphire, silicon (Si)(111), silicon carbide (SiC), *etc.*) through an epitaxial crystal growth method (*e.g.*, metal organic chemical vapor deposition (MOCVD), molecular beam epitaxy (MBE), *etc.*) and processing the epitaxial substrate thus grown, to form the desired structures.

Group III-nitride (III-N) compound semiconductor materials, including Ga_N, advantageously possess a wide band gap (or bandgap), a high breakdown electric-field, a large thermal conductivity, and excellent semiconductor behavior at temperatures exceeding 250 °C. In addition, a wide-bandgap heterostructure system, *e.g.*, incorporating an AlGa_N/Ga_N heterostructure enhanced by spontaneous and piezoelectric polarization effects, can yield a 2DEG channel with a high sheet charge concentration and high electron mobility, both of which lead to high current driving capability.

As such, Group III-nitride semiconductor materials, especially in the form of heterostructures, are favored candidates for fabricating power semiconductor devices. For example, III-nitride heterostructures can generate record output power densities at microwave and millimeter-wave frequencies. In addition, the III-nitride heterostructure devices, especially in the form of HEMT, are capable of delivering high operating frequency and high breakdown voltage simultaneously. Thus, the III-nitride heterostructure devices are also ideal candidates for the development of high-performance digital/analog mixed-signal integrated circuits.

AlGaIn/GaN HEMTs are suitable for high-power, high-frequency, and high-temperature operations, because of the material advantages and high density carriers in the 2DEG channel. The conventional Ga-face AlGaIn/GaN HEMT features strong spontaneous and piezoelectric polarization effect that results in very high 2DEG density in the range of approximately 10^{13} charges per square centimeter (cm^2) even without any intentional doping, which is an order of magnitude higher than those obtained in gallium arsenide (GaAs) and indium phosphide (InP) based HEMT structures that must feature intentional doping. Although the high 2DEG density is beneficial to achieving high current density and consequently, low on-resistance, it also results in a HEMT device that requires a negative gate bias to turn off the conduction current, thus, presenting the conventional AlGaIn/GaN HEMT devices as normally-on or depletion mode devices, which are defined as those with negative threshold voltage.

However, in circuit applications, normally-off or enhancement-mode HEMTs featuring positive threshold voltage are highly desirable because of simplified circuit configurations, reduced circuit complexity and simplified protection scheme. For instance, in radio-frequency (RF), microwave, and millimeter-wave circuits, normally-off devices enable the use of single-polarity (positive) supply voltage by eliminating the negative supply voltage. In GaN-based digital ICs, due to the lack of high-performance p-channel devices and low intrinsic hole mobility, CMOS-like implementation using p-channel and n-channel devices may not be a good choice. Instead, an all n-channel FET implementation strategy would be a needed for realizing high-performance (*e.g.*, high speed, high voltage swing, *etc.*). The direct coupled FET logic (DCFL) featuring E-mode FET as the driver and D-mode FET as the load is the simplest configuration for n-channel FET logic circuits. In addition, in power electronics application, normally-off devices are highly desirable because of their inherent fail-safe operation as the current conduction is naturally shut off in case the gate control is lost.

Various conventional techniques for fabricating normally-off AlGaIn/GaN HEMTs can include gate-recess by thinning down the gate barrier layer, fluorine plasma ion implantation by implanting fluorine ions into the gate barrier, use of thin gate barrier, and the use of p-type cap layer (*e.g.*, GaN or AlGaIn) or an InGaIn cap layer. However, these structures typically require sophisticated fabrication process techniques such as, for example, low-damage dry etching, F (fluorine) plasma

treatments, ion implantation, *etc.*, which typically rely on the principle of depleting the 2DEG in the channel at zero gate bias.

Another challenge in the implementation of conventional AlGa_N/Ga_N HEMTs is the relatively large off-state leakage current through the buffer layer, which could also result in premature breakdown in AlGa_N/Ga_N HEMTs. For instance, in conventional HEMTs, both the source and drain are typically formed by making ohmic contact to the 2DEG channel. However, if the buffer is leaky, the off-state source-drain leakage current will be large, leading to undesirable features such as large off-state power consumption. Conventional undoped Ga_N buffer layers, unfortunately, usually feature non-negligible leakage due to the high background doping (*e.g.*, by Si, (oxygen (O) impurities, *etc.*). Thus, sophisticated buffer techniques have been developed (*e.g.*, AlGa_N buffer, carbon (C) or iron (Fe) compensated doping in Ga_N) to suppress the leakage current that could otherwise result. It is thus desired to provide practical normally off HEMT devices with minimal off-state leakage current.

SUMMARY OF THE INVENTION

The following presents a simplified summary of the specification in order to provide a basic understanding of some aspects of the specification. This summary is not an extensive overview of the specification. It is intended to neither identify key or critical elements of the specification nor delineate any scope particular to any embodiments of the specification, or any scope of the claims. Its sole purpose is to present some concepts of the specification in a simplified form as a prelude to the more detailed description that is presented later.

In various embodiments, metal- 2DEG Schottky tunnel junctions can be employed in group III-Nitride field-effect devices that enable normally-off operation, large breakdown voltage, low leakage current, and high on/off current ratio. Accordingly, various embodiments provide structures, devices and methods for creating heterojunction AlGa_N/Ga_N metal two-dimensional electron gas (2DEG) tunnel-junction field-effect transistors (TJ-FET). As a further advantage, AlGa_N/Ga_N metal-2DEG TJ-FETs are disclosed that can be fabricated in a lateral configuration and/or a vertical configuration.

Accordingly, in exemplary non-limiting embodiments, a tunnel-junction field-effect transistor can comprise a substrate comprising a buffer layer deposited on the substrate and a barrier layer deposited on the buffer layer. In an aspect, the buffer layer and the barrier layer can form a heterojunction at an interface of the buffer layer and the barrier layer comprising a two-dimensional electron gas (2DEG) conducting channel. In addition, exemplary tunnel-junction field-effect transistors can comprise a metal region adjacent to the buffer layer, spanning a portion of the heterojunction, and in Schottky contact with the 2DEG conducting channel. In other embodiments, methodologies for forming a TJ-FET according is provided according to various aspects of the disclosed subject matter that include forming a metallic Schottky source contact to the 2DEG.

These and other additional features of the disclosed subject matter are described in more detail below.

BRIEF DESCRIPTION OF THE DRAWINGS

The devices, structures, and methodologies of the disclosed subject matter are further described with reference to the accompanying drawings in which:

FIGS. 1-6 depict various aspects of a non-limiting Aluminum-Gallium-Nitride (AlGaN)/Gallium-Nitride(GaN) metal two-dimensional electron gas (2DEG) tunnel junction field-effect transistors (TJ-FET) at different stages of an exemplary fabrication process;

FIG. 7 depicts exemplary non-limiting conduction band energy distribution profiles as a function of relative position (X) according to various aspects of the disclosed subject matter as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator;

FIG. 8 further illustrates exemplary non-limiting conduction band energy distribution profiles as a function of relative position (X) according to various aspects of the disclosed subject matter and as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator;

FIG. 9 further depicts aspects of exemplary non-limiting conduction band energy distribution profiles as a function of relative position (X) as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator;

FIG. 10 illustrates simulated and measured Schottky Barrier Height (SBH) at different gate bias for an exemplary AlGaIn/GaN metal-2DEG TJ-FET fabricated according to aspects of the disclosed subject matter and as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator;

5 FIGS. 11-20 depict or tabulate measured characteristics of an exemplary non-limiting implementation of an AlGaIn/GaN metal-2DEG TJ-FET according to various aspects of the disclosed subject matter;

FIG. 21 illustrates a cross section of an exemplary non-limiting III-nitride TJ-FET featuring a Schottky contact at both the source and drain electrodes according to
10 further aspects of the disclosed subject matter;

FIGS. 22-25 depict several cross-sections of further non-limiting vertical TJ-FET (VTJ-FET) structures in accordance with aspects of the disclosed subject matter;

FIGS. 26-33 depict various aspects of an exemplary non-limiting VTJ-FET as depicted in FIG. 22 at different stages of an exemplary fabrication process;

15 FIG. 34 depicts exemplary non-limiting methodologies for forming a TJ-FET in accordance with aspects of the disclosed subject matter;

FIG. 35 depicts further non-limiting methodologies for forming a TJ-FET in accordance with aspects of the disclosed subject matter and with reference to various non-limiting embodiments of FIGS. 1-6.

20 DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

Overview

As used herein, acronyms are used to denote the following: Source (S), Drain (D), Gate (G), Current (I), Voltage (V), Breakdown Voltage (BV), Transconductance (G_m), L (Length, Distance, or Spacing), X (Relative Position), ohmic Contact (O),
25 Anode (A), and Cathode (C) or Capacitance (C) as is apparent from the context.

The tunnel junction field effect transistor, typically used in Si CMOS, can also be employed in other narrow and medium bandgap semiconductor material systems such as silicon germanium (SiGe), gallium antimony (GaSb), *etc.* Such device structures are expected to be suitable for ultra short channel transistors due to the
30 scalable low-resistance contacts, low off-state leakage current, and suppressed drain induced barrier lowering (DIBL) effect or the so-called short channel effect. As can be understood, factors that affect the TJ-FET's characteristics include Schottky Barrier Height (SBH), and width between the source metal and the channel

semiconductor. In conventional Si TJ-FETs, low current drive capability has been observed unless SBH is made small even using low work function metal silicides featuring rare earth metal (such as erbium (Er), ytterbium (Yb), *etc.*). Although the low SBH can facilitate improved on-state current driving capability, such characteristics typically result in larger off-state leakage current. As a result, low tunneling barriers that facilitate devices' large on-state current can also degrade the devices' off-state performance. Consequently, even the best devices current drive level and on/off ratio obtained in Si tunnel junction FETs are approximately 10 mA/mm and 10^4 , respectively.

As described above, disclosed subject matter relates to group III-Nitride field-effect devices. Specifically, heterojunction AlGaIn/GaN metal-2DEG TJ-FET devices, structures, and related fabrication methodologies are disclosed. As described herein, the TJ-FET can be realized with a standard AlGaIn/GaN (high electron mobility transistor) HEMT structure, that can advantageously enable normally-off operation, large breakdown voltage, low leakage current, and high on/off current ratio. As a further advantage, AlGaIn/GaN metal-2DEG TJ-FETs are disclosed that can be fabricated in a lateral configuration and/or a vertical configuration.

As an example, III-Nitride devices, namely, AlGaIn/GaN metal-2DEG TJ-FETs are described and experimentally demonstrated. In aspect, a TJ-FET, when fabricated in an AlGaIn/GaN HEMT structure, can enable normally-off operation, low leakage current, and high on/off current ratio, due in part to an extremely high-density 2DEG (*e.g.*, $\sim 10^{13}/\text{cm}^2$) in Schottky contact to the source metal, forming a metal-2DEG Schottky, tunnel junction. As described herein, a Schottky junction featuring a thin Schottky barrier (*e.g.*, a few nanometers wide) can be provided to achieve a high tunneling coefficient and tunneling current. As a result, drain current density as high as several hundred of milliAmperes/millimeter (mA/mm) can be obtained.

In an aspect, exemplary TJ-FETs can include a stable source metal such as Ti, Al, Ni, Cr, resulting in devices that are easily manufactured. According to a further aspect, exemplary non-limiting implementations can be designed and fabricated without resort to the stringent requirements of high-quality low-leakage buffer layer(s) that can be required for suppressing off-state leakage current in conventional AlGaIn/GaN HEMTs or HFET. Advantageously, according to various embodiments, a Schottky metal source inherently can provide low leakage current (*e.g.*, as low as 1

nanoAmpere/mm (nA/mm)) at large drain bias (*e.g.*, 50 V). Thus, various embodiments can provide low off-state leakage current in high-voltage power switches. As a further advantage, various embodiments of the disclosed subject matter can provide a High I_{ON}/I_{OFF} ratio (*e.g.*, approximately 10^9). In yet another aspect, various embodiments of the disclosed subject matter can employ threshold voltage control scheme(s) different from that of a conventional HFET, which can add another degree of freedom in realizing normally-off GaN power transistors.

In this disclosure, GaN based AlGaN/GaN metal-2DEG tunnel junction FET structures, devices, and methods are described. Thus, according to various embodiments, normally-off operation AlGaN/GaN heterostructure devices and methods for fabrication thereof are provided. For instance, a normally-off operation AlGaN/GaN heterostructure in the form of metal-2DEG tunnel junction FET can be fabricated that has 2DEG in the channel that remains high at zero gate bias rather than depleting the 2DEG at zero gate bias. According to an aspect, III-nitride heterostructures (*e.g.*, AlGaN/GaN, AlN/GaN, InAlN/GaN) facilitate achieving high current drive capability.

As a result, these heterostructures can enable 2DEG channels with high electron density that cannot be achieved in other heterostructures (*e.g.*, AlGaAs/GaAs, AlGaAs/InGaAs, InAlAs/InGaAs, InAlSb/InSb, *etc.*). Accordingly, various non-limiting implementations of the disclosed subject matter can employ a high density 2DEG channel in Schottky contact with the source metal, resulting in a thin tunnel barrier (*e.g.*, the depletion region at the metal semiconductor junction) with high tunneling. Thus, in an aspect gate bias can control the effective tunnel barrier thickness as well as the barrier height.

In a further non-limiting aspect, the disclosed subject matter provides using metal as a drain electrode in addition to using metal as a source electrode. That is, drain electrode(s) can be formed by either ohmic contact or Schottky contact. It can be understood that while ohmic drain configuration can avoid voltage offset associated with the drain Schottky junction and maintains high current drive capability, the Schottky drain can provide a reverse drain blocking capability.

Exemplary Non-Limiting AlGaN/GaN metal-2DEG TJ-FETs

FIGS. 1-6 depict various aspects of a non-limiting Aluminum-Gallium-Nitride (AlGaN)/Gallium-Nitride(GaN) metal two-dimensional electron gas (2DEG) tunnel

junction field-effect transistors (TJ-FET) at different stages of an exemplary fabrication process. According to various embodiments, exemplary process steps can include active region isolation, drain electrode {*e.g.*, ohmic, Schottky, *etc.*) formation, source recess and metallization, gate dielectric layer deposition, and gate metallization.

5 Thus, FIG. 1 illustrates an exemplary starting wafer 100 for a non-limiting implementation of III-nitride metal-2DEG tunnel junction FET. For example, III-nitride metal-2DEG TJ-FET can typically be fabricated on a substrate 102 (*e.g.*, sapphire, Silicon (Si), Silicon Carbide (SiC), *etc.*) by growing III-nitride material buffer layer 104 (*e.g.*, GaN, AlN, AlGa_N, *etc.*), III-nitride semiconductor barrier layer
10 106 (*e.g.*, AlGa_N, InAlN, AlN, *etc.*), *etc.*, for example, via an epitaxial crystal growth method (*e.g.*, metal organic chemical vapor deposition (MOCVD), molecular beam epitaxy (MBE), *etc.*). Further processing the heterostructure (102/104/106) thus grown, can be performed to form the desired structures (*e.g.*, source, gate, and drain, *etc.*) as described below.

15 FIG. 2 illustrates an exemplary active region isolation process 200 that can be performed via mesa etching the heterostructure (102/104/106) used for AlGa_N/GaN metal-2DEG TJ-FET fabrication. For instance, a dry etching technique such as inductively coupled plasma reactive ion etching (ICP-RJE) can be performed to define active regions and form isolation regions between individual devices. The isolation
20 can also be performed by ion implanting the region outside the active device areas, for example, enabling a planar isolation.

FIG. 3 further illustrates a schematic cross-section 300 of an exemplary implementation of an AlGa_N/GaN metal-2DEG TJ-FET fabrication after formation of an ohmic drain contact 108. According to an aspect, an ohmic contact layer 108 can
25 be formed on the underlying III-nitride semiconductor barrier layer 106 (and hence underlying 2DEG between layer III-nitride semiconductor barrier layer 106 and III-nitride material buffer layer 104). According to a further non-limiting aspect, the ohmic drain contact 108 can comprise a metal stack (*e.g.*, comprising any of titanium (Ti), Al, Nickel (Ni) and gold (Au), *etc.*, or other compositions shown to be effective
30 in forming ohmic contact with low contact resistance). In yet another non-limiting aspect the evolving device can be thermally annealed (*e.g.*, thermally annealed at 850 degrees Celsius for 35 seconds, *etc.*).

FIG. 4 further depicts a schematic cross-section 400 of an exemplary AlGa_N/GaN Schottky metal-2DEG TJ-FET fabrication including formation of a

recessed source and a Schottky source contact 110. For instance, in forming the recessed source and Schottky source contact, dry etching techniques such as ICP-RIE or other etching techniques that create low-damage and nearly vertical sidewall profile can be performed to etch through the III-nitride semiconductor barrier layer 106 and define the source contact region. Subsequently, a metal layer 110 (*e.g.*, source contact 110) with single or multiple metal layers (*e.g.*, Ti, Al, chromium (Cr), Ni, platinum (Pt), Au, *etc.*) can be deposited on III-nitride material buffer layer 104 to form a Schottky contact to 2DEG. It should be noted that, according to various embodiments, the tunnel junction exists at the metal-2DEG junction.

FIG. 5 further illustrates a schematic cross-section 500 of the AlGaIn/GaN metal-2DEG TJ-FET after depositing gate insulating dielectric layer 112. According to various embodiments, gate insulating dielectric layer 112 or passivation layer can comprise a dielectric (*e.g.*, aluminum oxide (Al_2O_3), aluminum nitride (AlN), silicon nitride (SiN), silicon dioxide (SiO_2), hafnium dioxide (HfO_2), *etc.*) that can be grown or deposited on semiconductor layer III-nitride semiconductor barrier layer 106. In addition, wet etching such as a buffered oxide etch (BOE) or dry etch techniques can be performed to etch through gate insulating dielectric layer 112 to expose source (*e.g.*, Schottky source contact 110 region) and drain contact (*e.g.*, ohmic contact layer 108 region) regions.

FIG. 6 depicts a schematic cross-section of an exemplary AlGaIn/GaN metal-2DEG TJ-FET 600 after the formation of a gate electrode 602 and interconnects on the source contact 604 (*e.g.*, Schottky source contact 110 region) and drain contact 606 (*e.g.*, ohmic contact layer 108 region) regions. For instance, a gate metallization layer 114 can be formed by single or multiple metal layers (*e.g.*, including Al, Ti, Ni, Pt, Au, titanium nitride (TiN), titanium tungsten (TiW), *etc.*). According to various aspects, gate metallization layer 114 can be deposited on gate insulating dielectric layer 112, and can be further deposited on source (*e.g.*, Schottky source contact 110 region) and drain contact (*e.g.*, ohmic contact layer 108 region) regions to form source and drain interconnects as shown in FIG. 6. In yet other exemplary implementations, AlGaIn/GaN metal-2DEG TJ-FET can include passivation layer 116 which shall be formed with insulating dielectric materials such as SiN , SiO_2 , Al_2O_3 , polyimide, *etc.*

Accordingly, schematic structures of an exemplary non-limiting TJ-FET featuring a metal-2DEG tunnel junction at the source and an ohmic drain are depicted in FIGS. 1-6, according to various aspects. Thus, as described above, device

fabrication can begin with active region formation by mesa etching or ion implantation. Drain ohmic contact (*e.g.*, ohmic contact layer 108) can be formed by metal deposition (*e.g.*, Ti, Al, Ni, Au, *etc.*) followed by rapid thermal annealing (*e.g.*, thermal anneal at 850 degrees Celsius for 35 seconds). The source contact (*e.g.*, Schottky source contact 110) can then be formed by creating a shallow recess followed by source metal deposition. According to an aspect, the shallow recess should encroach on Ill-nitride material buffer layer 104 and Ill-nitride semiconductor barrier layer 106 sufficiently such that the 2DEG at the sidewall of the recess regions can be exposed and direct metal-2DEG contact can be enabled and obtained in Schottky source contact 110 region.

According to an aspect, source contact metals (*e.g.*, for Schottky source contact 110) are preferred that have relatively low work function (*e.g.*, Ti, Al, *etc.*) and good adherence (*e.g.*, Ti, Cr, Ni, Pt, *etc.*). According to an exemplary embodiment, a Ti-based metal composition (*e.g.* Ti Au, or Ti Al Ti Au) can be used. In a further non-limiting aspect, a thin layer of gate insulating dielectric layer 112 (*e.g.*, a few nanometers to a few tens of nanometer thick) of dielectric layer (Al_2O_3 , SiN, SiO_2 , HfO_2 , or stack of these dielectric materials) can be deposited (*e.g.*, by atomic layer deposition or other means such as plasma enhanced chemical vapor deposition (PE-CVD), sputtering, *etc.*). Thus, in further non-limiting aspects a gate electrode 602 (*e.g.*, Ni, Ti, Pt, and similar based metals, *etc.*) can be formed on top of the gate insulating dielectric layer 112. Note that in particular non-limiting embodiments there could be a small overlap between the gate 602 and source electrode 604 (not shown). In yet further non-limiting embodiments, the gate 602 and source electrodes 604 could also be self-aligned.

Thus, as can be seen in FIGS. 1-6, a conventional ohmic source contact can be replaced by Schottky metal source (Schottky source contact 110) in intimate contact with the 2DEG from the sidewall of recess in Ill-nitride material buffer layer 104 and Ill-nitride semiconductor barrier layer 106. As a result, according to various aspects, a normally-off Ill-nitride AlGaIn/GaN metal-2DEG TJ-FET can be created. Thus, according to various embodiments, the Schottky source contact 110 to 2DEG junction is naturally reverse biased under forward drain voltage, which can effectively block buffer leakage even for a selection of a leaky buffer layer (*e.g.*, Ill-nitride material buffer layer 104 selection is leaky). Accordingly, the disclosed TJ-FET structures and devices can provide a natural blocking capability to the buffer leakage problem.

In addition, it can be understood that under positive drain bias and zero gate bias, although the channel features high 2DEG density is capable of conducting current, the metal-2DEG junction is reverse biased. Advantageously, the reverse biased metal-2DEG junction features a tunnel junction with a barrier height (BH) and barrier width (BW) that, as long as the BH is high enough and BW is large enough, the tunneling current through the reverse-biased metal-2DEG junction is negligible and the transistor is in an "OFF" state. It can be further understood that as the gate bias is increased to positive value, the 2DEG density is further increased, which can lower the barrier height as a result of the mirror charge phenomenon and can reduce the barrier width as the conduction band in the 2DEG channel is pulled down. Both of these effects, when strong enough, can lead to the "turn-on" of the tunnel junction, and consequently, the current flow. Accordingly, a normally-off III-nitride field-effect transistor is provided in the form of metal-2DEG tunnel-junction FET as described.

As described above, with the high density 2DEG channel that is in Schottky contact with the source metal (*e.g.*, Schottky source contact 110), a thin tunnel barrier (the depletion region at the metal semiconductor junction) with high tunneling coefficient can be obtained. Thus, the gate bias can control the effective tunnel barrier thickness as well as the barrier height. For example, the operation principle can be further illustrated by a device simulation using 2-D simulator, as shown in FIG. 7-10.

For instance, FIG. 7 depicts exemplary non-limiting conduction band energy distribution profiles 700 as a function of relative position (X) according to various aspects of the disclosed subject matter as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator. FIG. 8 further illustrates exemplary non-limiting conduction band energy distribution profiles 800 as a function of relative position (X) according to various aspects of the disclosed subject matter and as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator. As can be seen in FIGS. 7-8, conduction band distribution profiles of TJ-FET are shown with the position of source-2DEG contact (*e.g.*, Schottky source contact 110) set to be at position $X=0$. Note that in FIGS. 7-8, the reference characters 702/802, 704/804, 706/806 correspond to different bias conditions: 702/802 ($V_{GS} = -3\text{ V}$, $V_{DS} = 10\text{ V}$), 704/804 ($V_{GS} = 0\text{ V}$, $V_{DS} = 10\text{ V}$), and 706/806 ($V_{GS} = 3\text{ V}$, $V_{DS} = 10\text{ V}$), respectively.

Thus, FIGS. 7-8 illustrate the conduction band profile in the 2DEG channel at different V_{DS} and V_{GS} bias by simulation. Curves 702/802 illustrate the conduction band profile at $V_{GS} = -3V$ and $V_{DS} = 10 V$. It can be seen from FIGS. 7-8 that the 2DEG channel is pinched-off in this situation. Curves 704/804 (*e.g.* zero gate bias) illustrate the conduction band profile at $V_{GS} = 0 V$ and $V_{DS} = 10 V$. In this situation, the 2DEG channel is not cut-off, but the effective tunnel barrier thickness can be seen to be larger than 10 nm, which suggests that the tunnel junction is turned off. Therefore the metal-2DEG TJ-FET's operation mode can be in enhancement mode in situation described by curves 704/804. Curves 706/806 illustrate the conduction band profile at $V_{GS} = 3V$ and $V_{DS} = 10 V$. Note that the effective source tunnel barrier thickness is smaller than 1 nm in this instance, and the transistor is turned on.

Thus, according to various embodiments, both low off-state leakage and high on-state current can be obtained. For example, at zero gate bias (704/804), the effective tunnel junction barrier thickness is 10 nm, which is large enough to block the electron tunneling from the source metal 808 (*e.g.*, Schottky source contact 110) at Fermi energy level (E_f) 810 to the 2DEG channel. At zero gate bias (704/804), as long as the 2DEG density is not extremely high, the effective tunnel barrier thickness will be large (*e.g.*, > 5 nm) and the tunneling coefficient is small, leading to negligible tunnel current. Thus, in this state, the exemplary devices can be said to be in the "OFF" state. However, at a gate bias of 3V (706/806), the effective barrier thickness is less than 1 nm, facilitating a large tunneling coefficient and a large tunneling current. Accordingly, at high gate bias, the effective barrier thickness is reduced as a result of the higher 2DEG density and tunneling coefficient leading to high tunnel current. Consequently, in this state, the exemplary devices can be said to be in the "ON" state.

In addition, in exemplary non-limiting TJ-FETs as described herein, the Schottky barrier height at the source metal-2DEG junction is not fixed, and thus, the Schottky barrier lowering effect should be considered. For instance, there exists a mirror-image force between electrons in the 2DEG channel and the positive image charge in the source metal (*e.g.*, Schottky source contact 110). With this mirror-image attraction force the conduction band energy near the Schottky contact (*e.g.*, Schottky source contact 110) could be lowered and therefore the Schottky barrier height is also lower, as shown in FIG. 9.

FIG. 9 further depicts aspects of exemplary non-limiting conduction band energy distribution profiles as a function of relative position (X) as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator. In FIG. 9 the conduction band distribution profiles of TJ-FET with 902 (dashed lines) and without 904 (solid lines) the Schottky barrier lowering effect at different gate bias (906, 908, 910) and $V_{DS} = 0$ V are shown, where $X = 0$ corresponds to the position of source-2DEG contact. It can be seen that with larger gate voltage, the mirror-image force at the Schottky contact (*e.g.*, Schottky source contact 110) generated by electrons in the 2DEG channel becomes larger and therefore the Schottky barrier height is lower.

It can be further understood that as the gate bias can affect electrons' density in the 2DEG channel, it can also affect the 2DEG-density-dependent Schottky barrier height. For instance, FIG. 10 illustrates measured 1002 and simulated 1004 Schottky Barrier Height (SBH) at different gate bias for an exemplary AlGaIn/GaN metal-2DEG TJ-FET (*e.g.*, a TJ-FET fabricated on a baseline AlGaIn/GaN HEMT structure) fabricated according to aspects of the disclosed subject matter as demonstrated by a device simulation for an exemplary TJ-FET using a 2-D simulator. Measured Schottky barrier heights can be extracted from temperature dependent positive biased Schottky source current-voltage (I-V) measurement results at different gate voltages. It can be seen that the Schottky barrier lowering effect shown in FIG. 9 does match the real device characteristics.

For example, at positive gate bias, the number of electrons is expected to be large and the mirror-image force stronger, resulting in a lower Schottky barrier height and larger tunneling coefficient. In contrast, at negative gate bias, electrons in the 2DEG channel are reduced or depleted, thus the mirror-charge effect is weaker and the Schottky barrier height is large enough to keep the device in "OFF" state.

Thus, it can be understood that the gate controlling mechanism in TJ-FET structure (*e.g.*, an exemplary TJ-FET fabricated on a baseline AlGaIn/GaN HEMT such as described with reference to FIGS. 1-6) is completely different from that of HEMTs. For example, in a conventional HEMT, gate bias depletes and induces 2DEG in the channel, creating the OFF/ON states. As described above, the strong polarization in III-nitride heterostructures (*e.g.*, AlGaIn/GaN) presents great challenge in realizing normally-off HEMT. However, in TJ-FETs, the threshold voltage is controlled by the tunnel barrier width via gate bias. Even with high 2DEG density, the

threshold voltage of TJ-FET could still be positive since the turn-on of the tunnel junction requires 2DEG density as high as $9 \times 10^{12}/\text{cm}^2$.

According to particular non-limiting embodiments, the disclosed subject provides a normally off metal-2DEG TJ-FET using a commercially available
 5 AlGaIn/GaN HEMT epitaxial wafer grown by MOCVD (*e.g.*, on a 4-inch (111) silicon substrate). For instance, according to an aspect, an epi-structure can comprise one or more of a GaN buffer layer, a 2 nm AlN interface enhancement layer, an undoped 17.5 nm $\text{Al}_{0.2}\text{Ga}_{0.8}\text{N}$ barrier layer, and a 2 nm undoped GaN cap layer. Accordingly, it is noted a typical starting wafer can yield a 2DEG density of
 10 $9 \times 10^{12}/\text{cm}^2$ with mobility of approximately $1600 \text{ cm}^2/\text{Vs}$, and a threshold voltage of -2.1 V.

The measured characteristics of a particular non-limiting TJ-FET are demonstrated in FIGS. 11-20. For instance, according to an aspect, typical exemplary TJ-FETs according to aspects of the disclosed subject matter can feature an $I_{\text{ON}}/I_{\text{OFF}}$
 15 ratio of 10^9 at forward drain bias up to 50 V, a maximum drain current density of 230 mA/mm at $V_{\text{GS}} = 3.5 \text{ V}$, a threshold voltage of +1.22 V, a sub-threshold slope (SS) of 89 mV/decade, reverse break down voltages (BV) of 274 V for a device with 2 μm gate-drain distance and 557 V for a device with 15 μm gate-drain distance (at 0.1 mA/mm leakage current). From FIG. 16, it can be seen that no drain offset voltage is
 20 presented as a result of using an ohmic drain instead of Schottky drain in a particular non-limiting aspect. In addition, transconductance as shown in FIG. 14, is nearly flat (or constant) after reaching the peak, indicating excellent linearity.

Accordingly, FIGS. 11-20 depict measured characteristics of an exemplary non-limiting implementation of an AlGaIn/GaN metal-2DEG TJ-FET according to
 25 various aspects of the disclosed subject matter. For instance, FIG. 11 depicts experimentally measured $I_{\text{D}}-V_{\text{GS}}$ profiles for an exemplary non-limiting TJ-FET (1102), an exemplary simulated TJ-FET (1104), and a conventional HEMT (1106) at $V_{\text{DS}} = 10 \text{ V}$, and fabricated on the same type of AlGaIn/GaN wafer with gate width $W_{\text{G}} = 10 \mu\text{m}$, gate length $L_{\text{G}} = 2 \mu\text{m}$, and gate-drain spacing $L_{\text{GD}} = 2 \mu\text{m}$. From FIG. 11,
 30 it can be seen that the measured results 1102 are in close agreement with the simulated results 1104 in terms of the gate turn-on voltage. In addition, the threshold voltage is positive, illustrating the TJ-FET's normally-off operation according to various embodiments.

The different threshold voltages in the TJ-FET (1102, 1104) and HEMT (1106) clearly exhibit the different mechanisms in the current turn-on. For instance, low off-state leakage current of 1×10^{-7} mA/mm (*e.g.*, approximately 1 picoAmpere (pA)) can be obtained with a maximum drain current of 230 mA/mm at $V_{DS} = 3.5$ V. In addition, the I_{on}/I_{off} ratio 1108 of TJ-FET 1102/1104 is 10^9 , or about three orders of magnitude higher than that 1110 (10^6) achieved in conventional a HEMT 1106 fabricated on the same epitaxial wafer. Thus, this clearly illustrates the advantageous leakage suppression by the reverse biased source Schottky junction. Further exemplary device performance characteristics for particular non-limiting implementations of an AlGaIn/GaN TJ-FET and a HEMT fabricated on the type same substrate are tabulated in FIG. 18.

FIG. 12 depicts the experimentally measured I_D - V_{GS} characteristics of an exemplary non-limiting TJ-FET at different V_{DS} (indicated as reference characters 1202-1212). Note that the off state leakage current exhibits little change as V_{DS} varies from 1 V to 50 V. Note that the off-state I_D keeps stable until V_{DS} is larger than 50 V (*e.g.*, when the gate insulator layer is expected to become leaky), indicating that the drain induced barrier lowering (DIBL) effect is sufficiently reduced.

FIG. 13 depicts the experimentally measured I_D - V_{GS} profiles of an exemplary non-limiting TJ-FET in linear scale at $V_{DS} = 10$ V. Note that the threshold voltage of TJ-FET is about +1.22 V, presenting the TJ-FET as a normally-off transistor. FIG. 14 depicts corresponding transconductance G_m - V_{GS} profiles of an exemplary non-limiting metal-2DEG TJ-FET with $W_G = 10$ μm , $L_G = 2$ μm and $L_{GD} = 2$ μm at $V_{DS} = 10$ V. Note that, according to an aspect, at $V_{DS} = 10$ V, G_m could be stabilized at 100-105 milliSiemens/mm (mS/mm) when V_{GS} is 2 V to 3.5 V, which indicates good linearity in input-output transfer relation.

FIG. 15 depicts the experimentally measured sub-threshold slope (SS) V_{GS} profiles of an exemplary non-limiting TJ-FET 1502 and a HEMT 1504 with gate width $W_G = 10$ μm , gate length $L_G = 2$ μm , and gate-drain spacing $L_{GD} = 2$ μm . TJ-FET 1502 shows significantly lower SS than the conventional HEMT. FIG. 16 depicts the experimentally measured I_D - V_{DS} profiles of an exemplary non-limiting TJ-FET with gate width $W_G = 10$ μm , gate length $L_G = 2$ μm , and gate-drain spacing $L_{GD} = 2$ μm .

FIG. 17 depicts the experimentally measured I_D - V_{DS} profiles of exemplary non-limiting TJ-FETs with a gate width $W_G = 10 \mu m$, a gate length $L_G = 2 \mu m$, and a gate-drain spacing $L_{GD} = 2, 5, 10$, and $15 \mu m$ at pinch-off, and with breakdown drain current limit of 0.1 mA/mm . It can be seen from FIG. 17 that at relatively short L_{GD} ($2 \mu m$) 1702, the exemplary TJ-FET delivers breakdown voltage more than 2 times of conventional HEMTs. This is due in part to the fact that the pinch-off in the exemplary TJ-FET starts at the source tunnel junction, while the pinch-off of HEMT starts at the gate edge at the drain side. Therefore, the effective distance between the starting pinch-off region and the drain terminal is larger in TJ-FET than in HEMT. When L_{GD} is larger (5 (1704), 10 (1706), and 15 (1708) μm), the difference of the breakdown voltage ($274V$, $369V$, $521V$, $557V$ for $L_{GD} = 2, 5, 10$, and 15 respectively) between an exemplary TJ-FET and HEMT becomes smaller. It is further noted that the specific on resistance (R_{ON}) of exemplary TJ-FETs with $L_{GD} = 2, 5, 10$ and $15 \mu m$ are measured to be 0.69 , 1.06 , 1.66 and $2.74 \text{ milliohm (m}\Omega\text{)}/\text{cm}^2$, respectively.

FIG. 18 depicts the break down voltage comparison between an exemplary non-limiting TJ-FET 1802 and a conventional HEMT 1804 fabricated on the same AlGaIn/GaN wafer with different L_{GD} . In addition, FIG. 18 tabulates 1806 exemplary device performance characteristics for particular non-limiting implementations of an AlGaIn/GaN TJ-FET and a HEMT fabricated on the type same substrate. FIG. 19 demonstrates the trade-off characteristics 1900 between specific on-resistance R_{ON} and breakdown voltage of an exemplary non-limiting AlGaIn/GaN TJ-FET with different L_{GD} , in comparison with the theoretical Si (1902), SiC (1904) and GaN (1906) limits. FIG. 20 illustrates the experimentally measured current gain cutoff frequency f_{2002} and power gain cutoff frequency f_{max} 2004 of an exemplary non-limiting TJ-FET with gate width $W_G = 100 \mu m$, gate length $L_G = 2 \mu m$, and gate-drain spacing $L_{GD} = 2 \mu m$. For instance, with $L_G = 2 \mu m$, the maximum f_T is 6.3 GHz and the maximum f_{max} is 15.3 GHz .

While the disclosed subject matter has been described above in connection with various embodiments, it is to be understood that other similar embodiments may be used with, or modifications and additions may be made to, the described embodiments for performing the same or similar functions as described herein without deviating from the disclosed subject matter.

Further Non-Limiting Embodiments of TJ-FETs

In a further non-limiting aspect, the disclosed subject matter provides using metal as a drain electrode in addition to using metal as a source electrode. That is, drain electrode(s) can be formed by either ohmic contact or Schottky contact. It can be understood that while ohmic drain configuration can avoid voltage offset associated with the drain Schottky junction and maintains high current drive capability, the Schottky drain can provide a reverse drain blocking capability.

For example, FIG. 21 illustrates a schematic cross section of further non-limiting Ill-nitride TJ-FET 2100 featuring a Schottky contact at both the source (Schottky source contact 2102) and drain electrodes (Schottky drain contact 2104) according to further aspects of the disclosed subject matter. For ease of explanation and not limitation, FIG. 21 uses similar nomenclature as that for FIGS. 1-6 to depict similar functional characteristics or features as that described above, for example, regarding FIGS. 1-6, *etc.* Using terminology similar to that of FIGS. 1-6, while highlighting features of the various embodiments set forth herein, FIG. 21 depicts a cross-section of Schottky drain TJ-FET 2100. For instance, as compared to the ohmic drain TJ-FET 600 of FIG. 6, Schottky drain TJ-FET 2100 can include metallization of the drain electrode.

For example, as can be seen in FIG. 21, the symmetrical metal-2DEG source metal-2DEG drain tunnel junction FET features metal-2DEG junctions at both the source 2102 and drain 2104 electrodes. This device features a metal layer 2106 (*e.g.*, with single or multiple metal layers of one or more of Ti, Al, Cr, Ni, Pt, Au, *etc.*) used for source 2102 and drain 2104 electrodes. In a non-limiting aspect, the prospective source 2102 and drain 2104 regions can be recessed to semiconductor layer 104 by dry or wet etching techniques, before the metal deposition. It can be understood that according to various embodiment as described herein, such source 2102 and drain 2104 metallic electrodes are in Schottky contact with the 2DEG to form both source 2102 and drain 2104 contacts.

It should be noted that yet other configurations, arrangements, structures, and embodiments are possible according to the disclosed subject matter. For example, the exemplary TJ-FETs described above relate to lateral device construction and operation in which the current path is exemplified by traveling through the source metal-2DEG tunnel junction and the 2DEG channel. According to various aspects, TJ-FETs can also be implemented according to vertical structures and operation, in

which the drain terminal is formed to a conducting layer under the 2DEG channel, but separated from the 2DEG channel (*e.g.*, by an undoped GaN spacer, a lightly doped acceleration layer, *etc.*) as described below.

For instance, according to further non-limiting implementations, a tunnel
5 junction FET can also be implemented in a vertical structure, for example, with the drain electrode contacting a nitride semiconductor layer located below the heterojunction. In such a non-limiting example, the current flow path can comprise lateral tunneling through a metal-2DEG junction and vertically transporting through a spacer layer. It can be understood that a major advantage of a vertical tunnel junction
10 FET is the elimination of current collapse, which can occur in lateral devices such as AlGaIn/GaN HEMT as a result of the surface states in the gate-drain region.

As further examples, FIGS. 22-25 depict several cross-sections of further non-limiting vertical TJ-FET (VTJ-FET) structures in accordance with aspects of the disclosed subject matter. For instance, FIG. 22 shows the schematic cross-section of
15 an exemplary vertical tunnel junction field effect transistors (VTJ-FET) 2200 realized on III- nitride semiconductor materials, having drain electrodes located at the front side of the starting wafer.

Using terminology similar to that of FIGS. 1-6, and 21, while highlighting features of the various embodiments set forth herein FIG. 22 depicts a substrate layer
20 2202 (*e.g.*, Si, SiC, Sapphire, or GaN, *etc.*) upon which can be formed a group III-nitride material layer 2204 (*e.g.*, n-type heavily doped GaN in the range of 10^{18} cm^{-3} or higher, *etc.*). According to a non-limiting aspect, a first nitride semiconductor layer 2206 (*e.g.*, n-type lightly-doped GaN in the range of 10^{16} cm^{-3}) can be formed on the group III-nitride material layer 2204. In a further aspect, a second nitride
25 semiconductor layer 2208 (*e.g.*, undoped GaN, *etc.*) can be formed on the nitride semiconductor layer 2206. According to further non-limiting implementations, a nitride semiconductor barrier layer 2210 (*e.g.*, $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 < x \leq 1$)) can be formed on second nitride semiconductor layer 2208. It can be understood that a polarization charge can generated by spontaneous and piezoelectric polarization of the nitride
30 semiconductor material, at the interface between second nitride semiconductor layer 2208 and nitride semiconductor barrier layer 2210.

As a result of the polarization charge, a 2DEG 2212 can be formed in the vicinity between second nitride semiconductor layer 2208 and nitride semiconductor

barrier layer 2210. In further non-limiting implementations, a source contact 2214 {*e.g.*, a Schottky contact) can be formed in the recessed region of nitride semiconductor barrier layer 2210 and second nitride semiconductor layer 2208. In addition, according to a further aspect, a dielectric layer (*e.g.*, gate insulating dielectric layer 2216), such as, for example, silicon nitride, aluminum oxide, *etc.*, can be formed on the nitride semiconductor barrier layer 2210 and source contact 2214.

In yet other aspects, non-limiting implementations of an exemplary VTJ-FET can comprise a gate contact layer (*e.g.*, gate metallization layer 2218, *etc.*), such as, for example, a Ni and Au metal stack, that can be formed on the dielectric layer (*e.g.*, gate insulating dielectric layer 2216). In further exemplary embodiments, a drain contact layer 2220, such as, for example, an ohmic metal stack comprising any combination of Ti, Al, Ni, and Au, and so on, can be formed on the concaved surface of group III-nitride material layer 2204. In still other non-limiting implementations, a passivation or protection layer (*e.g.*, passivation layer 2222, *etc.*), such as, for example, a passivation layer comprised of SiN, can be formed on the exposed device surface, such as on exposed surfaces of one or more of group III-nitride material layer 2204, first nitride semiconductor layer 2206, second nitride semiconductor layer 2208, and nitride semiconductor barrier layer 2210, *etc.*

As another example, FIG. 23 illustrates a schematic cross-section of an exemplary tunnel junction field effect transistors (VTJ-FET) 2300 having drain electrodes located at the backside of an etched substrate layer. For instance, according to a particular non-limiting implementation, the VTJ-FET 2300 of FIG. 23 can comprise analogous structures as that for VTJ-FET 2200, except for the formation of a drain contact layer 2302. Accordingly, for ease of explanation and not limitation, FIG. 23 uses similar reference characters and/or nomenclature as that for FIG. 22 to depict similar functional characteristics or features as that described above, for example, regarding FIGS. 1-6, 22, *etc.*

Thus, for VTJ-FET 2300, a drain contact layer (*e.g.*, ohmic drain contact 2302), such as a Ti, Al, Ni, Au ohmic metal stack, for example, can be formed on a back surface of group III-nitride material layer 2204. Drain contact layer (*e.g.*, ohmic drain contact 2302), according to an aspect, can also touch the exposed surface of substrate 2202 layer. It can be understood that one approach to form the drain contact layer (*e.g.*, ohmic drain contact 2302) related concave region is to remove substrate

2202 layer and part of group III-nitride material layer 2204, using masked wet or dry etching, as a non-limiting example.

As a further non-limiting example of VTJ-FET structures, FIG. 24 depicts a schematic cross-section of an exemplary VTJ-FET 2400 having drain electrodes (*e.g.*, ohmic drain contact 2402) located at the bottom of the substrate 2404. As described above, FIG. 24 uses similar reference characters and/or nomenclature as that for FIGS. 22-23 to depict similar functional characteristics or features as that described above, for example, regarding FIGS. 1-6, 22-23, *etc.*, for ease of explanation and not limitation.

Accordingly, FIG. 24 illustrates VTJ-FET 2400 employing group III-nitride material layer 2404 to serve as a substrate. For example, in various embodiments, VTJ-FET 2400 can employ an n-type heavily doped GaN (*e.g.*, doped in the range of 10^{18} cm^{-3} or higher, *etc.*) group III-nitride material layer 2404. In a further aspect, a first nitride semiconductor layer 2406 (*e.g.*, an n-type lightly-doped GaN in the range of 10^{16} cm^{-3}) can be formed on the group III-nitride material substrate layer 2404. A second nitride semiconductor layer 2408 (*e.g.*, such as undoped GaN) can be formed on first nitride semiconductor layer 2406.

In yet another aspect, VTJ-FET 2400 can comprise a nitride semiconductor barrier layer 2410 (*e.g.*, a barrier layer comprised of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 < x \leq 1$)), which can be formed on second nitride semiconductor layer 2408, as described above. As further described above, it can be understood that a polarization charge can be generated by spontaneous and piezoelectric polarization of the nitride semiconductor material, at an interface at the boundary between second nitride semiconductor layer 2408 and nitride semiconductor barrier layer 2410. As a result of the polarization charge, a two dimensional electron gas (2DEG) 2412 can form in the vicinity between second nitride semiconductor layer 2408 and nitride semiconductor barrier layer 2410. According to yet another aspect, a source contact 2414 (*e.g.*, a Schottky contact, *etc.*) can be formed in the concave region of second nitride semiconductor layer 2408 and nitride semiconductor barrier layer 2410.

In addition, according to various embodiments a gate insulating dielectric layer 2416 (*e.g.*, a SiN , Al_2O_3 , dielectric layer *etc.*) can be formed on nitride semiconductor barrier layer 2410 and source contact 2414, as further described above. In various non-limiting implementations, VTJ-FET 2400 can further comprise a gate

contact layer {e.g., gate metallization layer 2418, etc.}, such as described above {e.g., a Ni, Au metal stack} that can be formed on gate insulating dielectric layer 2416.

Furthermore, a drain contact layer {e.g., ohmic drain contact 2402} can be formed on the backside of group III-nitride material substrate layer 2404 {e.g., an ohmic metal stack such comprised of any combination of Ti, Al, Ni, Au, etc.}. In further non-limiting implementations, a passivation or protection layer {e.g., passivation layer 2422, such as SiN, etc.} can be formed on one or more exposed device surfaces, such as nitride semiconductor barrier layer 2410.

In yet another non-limiting example of VTJ-FET structures, FIG. 25 depicts a schematic cross-section of an exemplary VTJ-FET 2500 including a trench region comprising a portion of the associated gate electrode. For instance, according to further non-limiting implementations, VTJ-FET 2500 of FIG. 25 can comprise analogous structures as that for VTJ-FET 2200, except for the formation of a trench region comprising a portion of the associated gate electrode. Accordingly, for ease of explanation and not limitation, FIG. 25 uses similar reference characters and/or nomenclature as that for FIG. 22 to depict similar functional characteristics or features as that described above, for example, regarding FIGS. 1-6, 22, 23, etc.

As an example, FIG. 25 illustrates VTJ-FET 2500 having a portion of gate layer {e.g., gate metallization layer 2218 such as a Ni, Au metal stack, etc.} formed on a concave surface of nitride semiconductor barrier layer 2210 and a portion of second nitride semiconductor layer 2208. In addition, gate insulating layer {e.g., gate insulating dielectric layer 2216, such as an Al_2O_3 layer, etc.} can be formed between second nitride semiconductor layer 2208 and nitride semiconductor barrier layer 2210 and gate contact layer {e.g., gate metallization layer 2218}. In a particular non-limiting implementation, a trenched region related to gate contact layer {e.g., gate metallization layer 2218} can be formed by removing portions of nitride semiconductor barrier layer 2210 and portions of second nitride semiconductor layer 2208, for example, using masked wet or dry etching. In further exemplary embodiments, a drain contact layer 2220, such as, for example, an ohmic metal stack comprising any combination of Ti, Al, Ni, and Au, and so on, can be formed on the concaved surface of group III-nitride material layer 2204.

Thus, it can be understood that for VTJ-FET 2300 and 2400 as depicted in FIGS. 23 and 24 respectively, part of gate contact layer {e.g., gate metallization layer 2218 and 2418} can also be formed on the concaved surface of nitride semiconductor

barrier layer 2210 (nitride semiconductor barrier layer 2410 for VTJ-FET 2400) and part of second nitride semiconductor layer 2208 (second nitride semiconductor layer 2408 for VTJ-FET 2400). Advantageously, a trenched gate facilitates clamping (or fixing) of potential along the walls of the trenched region, which can beneficially result in the depletion of the region between the trenched-gate and source contacts. Thus, this depletion of the region between the trenched-gate and source contacts can result in enhanced off-state blocking capability.

Accordingly, the disclosed subject matter provides tunnel-junction field-effect transistors TJ-FETs (*e.g.*, a normally-off III-nitride AlGaIn/GaN metal-2DEG TJ-FET 600, 2100 2200, 2300, 2400, 2500, *etc.*). According to an aspect, the TJ-FETs can comprise a substrate (*e.g.*, substrate 102, 2202, 2404, *etc.*). For instance, as described above, suitable substrates can comprise sapphire, silicon (111), silicon carbide (SiC), aluminum nitride (AlN), or GaN, with or without a nucleation layer such as a nucleation layer comprised of a group III-nitride. For instance, in a particular non-limiting implementation, a TJ-FET can comprise a sapphire substrate.

In addition, exemplary TJ-FETs can include a buffer layer (*e.g.*, III-nitride material buffer layer 104, first and second nitride semiconductor layers 2206/2208 (2406/2408), *etc.*) disposed or deposited on the substrate and a barrier layer a barrier layer (*e.g.*, III-nitride semiconductor barrier layer 106, nitride semiconductor barrier layer 2210/2410, *etc.*) disposed or deposited on the buffer layer. According to various aspects, the buffer layer and the barrier layer can form a heterojunction at an interface of the buffer layer and the barrier layer, as further described above. In addition, the heterojunction can comprise a 2DEG conducting channel (*e.g.*, a 2DEG conducting channel proximate to the prospective location for the gate).

In addition, exemplary TJ-FETs can further comprise a metal region adjacent to the buffer layer, proximate to the prospective location for the source, and spanning a portion of the heterojunction. For instance, regarding FIG. 6, 21-25, 33, *etc.* and related descriptions, as described above, the metallic Schottky source contact (*e.g.*, Schottky source contact 110, source contact 2214/2414, *etc.*) can be deposited on the buffer layer and in Schottky contact to 2DEG. Thus, as further described above, the metallic source contact in Schottky contact with the 2DEG at the heterojunction can be said to span a portion of the heterojunction.

Still other non-limiting implementations of TJ-FETs can include an insulating dielectric layer (*e.g.*, gate insulating dielectric layer 112, gate insulating dielectric

layer 2216/2416, *etc.*) deposited above the barrier layer (*e.g.*, Ill-nitride semiconductor barrier layer 106, nitride semiconductor barrier layer 2210/2410, *etc.*) proximate to the prospective location for the gate. In various embodiments, as described above, a gate (*e.g.*, gate 602, *etc.*) can be formed above the insulating dielectric layer (*e.g.*, gate insulating dielectric layer 112, gate insulating dielectric layer 2216/2416, *etc.*).

As further described herein, the gate can be further adapted to partially overlay a portion of the metal region proximate to the prospective location for the source (*e.g.*, the metallic Schottky source contact, Schottky source contact 110, source contact 2214/2414, *etc.*) and electrically isolated from the metal region by the insulating dielectric layer. In yet other embodiments (*e.g.*, VTJ-FET 2500) the gate can be further adapted to at least partially fill a trench etched in a portion of the barrier layer. In addition, according to various embodiments as described above, the drain with a TJ-FET can span a portion of the heterojunction and can be in at least one of ohmic contact or Schottky contact with the 2DEG. In other embodiments, (*e.g.*, VTJ-FETs) the drain can be electrically coupled to the Schottky source across the heterojunction.

In yet other non-limiting implementations, normally-off metal two-dimensional electron gas tunnel-junction field-effect transistors TJ-FETs (*e.g.*, a normally-off Ill-nitride AlGaIn/GaN metal-2DEG TJ-FET 2200, 2300, 2400, 2500, 3300, *etc.*) are provided that can comprise a second nitride semiconductor layer (*e.g.*, second nitride semiconductor layer 2208/2408) deposited on a first nitride semiconductor layer (*e.g.*, first nitride semiconductor layer 2206/2406). As a further example, such exemplary TJ-FETs can include a nitride semiconductor barrier layer (*e.g.*, nitride semiconductor barrier layer 2210/2410) deposited on the second nitride semiconductor layer (*e.g.*, second nitride semiconductor layer 2208/2408) and forming a heterojunction comprising a two-dimensional electron gas (2DEG) at an interface of the nitride semiconductor barrier layer and the second nitride semiconductor layer as described above.

In yet other non-limiting embodiments, the TJ-FETs can include one or more metallic source contact(s) associated with the metal-2DEG TJ-FET and in Schottky contact with the 2DEG. In still other implementations, the TJ-FETs can include one or more of an ohmic contact (*e.g.*, ohmic drain contact 2220/2302/2402, *etc.*) or a Schottky drain contact electrically coupled to the one or more metallic source contact(s) across the heterojunction.

In view of the structures and devices described *supra*, methodologies that can be implemented in accordance with the disclosed subject matter will be better appreciated with reference to the flowcharts of FIGS. 34-35. While for purposes of simplicity of explanation, the methodologies are shown and described as a series of blocks, it is to be understood and appreciated that such illustrations or corresponding descriptions are not limited by the order of the blocks, as some blocks may occur in different orders and/or concurrently with other blocks from what is depicted and described herein. Any non-sequential, or branched, flow illustrated *via* a flowchart should be understood to indicate that various other branches, flow paths, and orders of the blocks, can be implemented which achieve the same or a similar result. Moreover, not all illustrated blocks may be required to implement the methodologies described hereinafter.

Exemplary Methodologies

FIGS. 26-33 depict various aspects of an exemplary non-limiting VTJ-FET, for example, such as exemplary VTJ-FET depicted in FIG. 22 at different stages of an exemplary fabrication process. It should be understood that the various stages are depicted for ease of explanation and not limitation. For instance, it can be understood that such illustrations or corresponding descriptions are not limited by the number, order, or lack of inclusion of particular stage, as some stages may occur in different orders and/or concurrently with other stages from what is depicted and described herein. In other instances, suitable alternatives or arrangements for fabricating a particular feature or accomplishing a particular function can be devised that can be substituted for one or more stages or added thereto. Accordingly, the following description is merely intended to describe a subset of possible alternatives enabled by the disclosed structures, devices, and methodologies as described herein.

As a non-limiting example, FIG. 26 shows an example of the starting sample wafer, including a substrate 2202, a group III-nitride material layer 2204, a first nitride semiconductor layer 2206, a second nitride semiconductor layer 2208, and a nitride semiconductor barrier layer 2210, for example, as previously described in reference to FIG. 22.

In a further non-limiting implementation as depicted in FIG. 27, one or more active regions can be defined, for example, by dry etching *fe.g.*, dry etching using Chlorine/Helium (Cl₂/He) inductively coupled plasma reactive ion etching (ICP-RIE),

etc.). According to an aspect, dry etching can remove selected portions of nitride semiconductor barrier layer 2210, second nitride semiconductor layer 2208, first nitride semiconductor layer 2206, and group III-nitride material layer 2204 outside the active region. In a further aspect, in another region outside the active region, the surface of group III-nitride material layer 2204 can be exposed, upon which, the ohmic drain contact 2220 metallization can be formed. For instance, in yet another non-limiting example, in FIG. 28, ohmic drain contacts 2220 can be formed by metal deposition, for example, such as by electron-beam (e-beam) evaporation of any combination of Ti, Al, Ni, Au, *etc.* (*e.g.*, metal deposition of 20 nm, 150 nm, 50 nm, 80 nm, of Ti, Al, Ni, Au, respectively, and so on) followed by rapid thermal annealing (RTA) (*e.g.*, thermal anneal at 850 °C for 35 seconds, *etc.*).

According to a further non-limiting aspect, in FIG. 29, the source regions can be defined for example, with photo resist layer 2902. For instance, in the source regions, nitride semiconductor barrier layer 2210, and part of second nitride semiconductor layer 2208 can be removed, for instance, using a Cl₂/He plasma dry etch process in an ICP-RIE system. In a further aspect, etching depth can be pre-selected to just reach second nitride semiconductor layer 2208 and to expose the surface of second nitride semiconductor layer 2208 and the 2DEG 2212 (from the side as indicated in FIG. 29 by reference character 2904) in preparation for source contact 2214 metallization. In various embodiments, photo resist layer 2902 can be kept on the developing device 2900 until after source contact 2214 layer deposition and lift-off.

In FIG. 30, according to an aspect, the source contact 2214 electrodes can be formed by metal deposition. For instance, source contact 2214 electrodes can be formed by an electron-beam evaporated metal source (*e.g.*, an Al source, *etc.*) to deposit a predetermined thickness (*e.g.*, approximately 30 nm) defined by the photo resist layer 2902 shown in FIG. 29, which resist can be subsequently removed during lift-off. In various embodiments, the source contacts 2214 layer can contact the edge of nitride semiconductor barrier layer 2210 and second nitride semiconductor layer 2208, and the 2DEG 2212.

Referring to FIG. 31, in yet other exemplary embodiments, a thin (*e.g.*, approximately 10 nm, *etc.*) gate insulating dielectric layer 2216 can be grown by, for example, atomic layer deposition (ALD) or other deposition methods (*e.g.*, PE-CVD, sputtering, *etc.*) over nitride semiconductor barrier layer 2210, source contacts 2214

or portions thereof. From FIG 31 it can be seen that gate insulating dielectric layer 2216 can cover nitride semiconductor barrier layer 2210, source contacts 2214, or portions thereof. In further embodiments, for example as depicted in FIG. 32, a gate metallization layer 2218 can be used to form gate contact electrodes (*e.g.*, by deposition of electron-beam evaporated Ni and Au), *etc.* In a further non-limiting aspect as depicted in FIG. 33, a passivation layer 2222 (*e.g.*, a silicon nitride (SiN_x) passivation layer) can be deposited to protect the exposed device surface (*e.g.*, such as by PE-CVD).

It can be understood that for VTJ-FET 2300 and VTJ-FET 2400, fabrication stages as described above for VTJ-FET 2200 generally are generally applicable, except for the formation of ohmic drain contact 2302 in VTJ-FET 2300 and ohmic drain contact 2402 in VTJ-FET 2400. Thus, in fabricating VTJ-FET 2300, before the formation of ohmic drain contact 2302, concaved regions can be formed, and in these concaved regions, portions of substrate 2202 and group III-nitride material layer 2204 can be removed as indicated. Accordingly, the back surface of group III-nitride material layer 2204 can be exposed, to enable ohmic drain contact 2302 metallization. As a non-limiting example, the concave regions can be formed via a Cl₂/He plasma dry etch in an ICP-RIE system. Likewise, in fabricating VTJ-FET 2400, ohmic drain contact 2402 can be directly formed on the bottom of group III-nitride material substrate layer 2404.

FIG. 34 depicts exemplary non-limiting methodologies 3400 for forming a TJ-FET (*e.g.*, a normally-off III-nitride AlGaIn/GaN metal-2DEG TJ-FET 600, 2100, 2200, 2300, 2400, 2500, *etc.*) in accordance with aspects of the disclosed subject matter. For instance, at 3402, methodologies 3400 can comprise, for example, depositing a buffer layer (*e.g.*, III-nitride material buffer layer 104, first and second nitride semiconductor layers 2206/2208 (2406/2408), *etc.*) over a substrate (*e.g.*, substrate 102, 2202, 2404, *etc.*) as described above regarding FIGS. 1-6, for example. For instance, depositing a buffer layer over a substrate can include growing the buffer layer over one or more of a sapphire substrate, a silicon (111) substrate, a silicon carbide (SiC) substrate, an aluminum nitride (AlN) substrate, or a Gallium Nitride (GaN) substrate. Furthermore at 3402, depositing a buffer layer can comprise growing the buffer layer over the substrate having a III-nitride nucleation layer, as further described above.

In addition, at 3404, a barrier layer (*e.g.*, III-nitride semiconductor barrier layer 106, nitride semiconductor barrier layer 2210/2410, *etc.*) can be deposited over the buffer layer (*e.g.*, III-nitride material buffer layer 104, first and second nitride semiconductor layers 2206/2208 (2406/2408), *etc.*) to form a heterojunction comprising a 2DEG. For instance, as described above, an AlGaIn/GaN heterojunction can comprise a high density of carriers in the 2DEG channel.

In further non-limiting aspects of methodologies 3400, a metallic Schottky source contact (*e.g.*, Schottky source contact 110, source contact 2214/2414, *etc.*) can be formed to the 2DEG. Accordingly, various non-limiting methodologies 3400, the disclosed subject matter can employ a high density 2DEG channel as described herein in Schottky contact with the source metal (*e.g.*, Schottky source contact 110, source contact 2214/2414, *etc.*), resulting in a thin tunnel barrier (*e.g.*, the depletion region at the metal semiconductor junction) with high tunneling coefficient.

In addition, at 3408 fabrication of the TJ-FET device can be completed. For instance, as described above regarding FIGS. 1-6, 21-33, *etc.*, various fabrication stages can be employed to complete fabrication of the TJ-FET device. For instance, various etch, deposition, passivation, photolithography and other fabrication stages (clean, inspect, defect metrology, *etc.*) can be performed as described above regarding TJ-FET 600, 2100, 2200, 2300, 2400, 2500, 3300, and so on. For example, regarding VTJ-FET 2500, a portion of the barrier layer 2210 proximate to the design location for the gate 2218 can be etched as described above regarding FIG. 25.

As a further example, methodologies 3400 can further include growing a gate insulating dielectric layer (*e.g.*, gate insulating dielectric layer 112, gate insulating dielectric layer 2216/2416, *etc.*) above the barrier layer (*e.g.*, III-nitride semiconductor barrier layer 106, nitride semiconductor barrier layer 2210/2410, *etc.*) proximate to the design location for the gate (*e.g.*, 602, *etc.*). In further non-limiting methodologies, a metallic gate (*e.g.*, 602, *etc.*) can be formed over the gate insulating dielectric layer (*e.g.*, gate insulating dielectric layer 112, gate insulating dielectric layer 2216/2416, *etc.*) to partially overlay a portion of the metallic Schottky source contact. According to various embodiments, the metallic gate (*e.g.*, 602, *etc.*) is electrically isolated from the source metal (*e.g.*, Schottky source contact 110, source contact 2214/2414, *etc.*) by the gate insulating dielectric layer (*e.g.*, gate insulating dielectric layer 112, gate insulating dielectric layer 2216/2416, *etc.*).

In still other non-limiting methodologies 3400, a drain contact (*e.g.*, ohmic contact layer 108, ohmic drain contact 2220/2302/2402) can be formed in ohmic contact and/or in Schottky contact 2104 with the 2DEG. For instance, regarding FIGS. 22-33 and VTJ-FETs, a drain contact can be formed electrically coupled to the metallic Schottky source contact (*e.g.*, Schottky source contact 110, source contact 2214/2414, *etc.*) across the heterojunction formed by a barrier layer (*e.g.*, Ill-nitride semiconductor barrier layer 106, nitride semiconductor barrier layer 2210/2410, *etc.*) and the buffer layer (*e.g.*, Ill-nitride material buffer layer 104, first and second nitride semiconductor layers 2206/2208 (2406/2408), *etc.*).

FIG. 35 depicts further non-limiting methodologies 3500 for TJ-FET fabrication (*e.g.*, for fabricating a normally-off Ill-nitride AlGa_N/Ga_N metal-2DEG TJ-FET 600, *etc.*) in accordance with aspects of the disclosed subject matter and with reference to various non-limiting embodiments of FIGS. 1-6 (*e.g.*, a normally-off Ill-nitride AlGa_N/Ga_N metal-2DEG TJ-FET 600, *etc.*). For example, at 3502, a device can be isolated on a heterostructure. For instance, as described above, FIG. 2 illustrates an exemplary active region isolation process that can be performed via mesa etching the heterostructure (102/104/106) used for AlGa_N/Ga_N metal-2DEG TJ-FET fabrication.

Non-limiting methodologies 3500 can further include forming, at 3504, an ohmic drain contact on the heterostructure as described above regarding FIG. 3. For example, FIG. 3 further illustrates a schematic cross-section 300 of an exemplary implementation of an AlGa_N/Ga_N metal-2DEG TJ-FET fabrication after formation of an ohmic drain contact 108. In a non-limiting aspect, an ohmic contact layer 108 can be formed on the underlying Ill-nitride semiconductor barrier layer 106 (and hence underlying 2DEG between Ill-nitride semiconductor barrier layer 106 and Ill-nitride material buffer layer 104). In a further non-limiting aspect, the ohmic drain contact 108 can comprise a metal stack (*e.g.*, comprising any of Ti, Al, Ni and Au, *etc.*, or other compositions shown to be effective in forming ohmic contact with low contact resistance). In yet another non-limiting aspect the evolving device can be thermally annealed (*e.g.*, thermally annealed at 850 degrees Celsius for 35 seconds, *etc.*). According to various embodiments, an ohmic contact layer 108 as described herein can advantageously eliminate the voltage offset that would otherwise occur with the use of a Schottky drain contact.

In a further non-limiting aspect, at 3506, non-limiting methodologies 3500 can further include creating a source recess to expose 2DEG as further described above. In addition, at 3508 methodologies 3500 can include forming a Schottky source in contact with the 2DEG. For instance, FIG. 4 further depicts a schematic cross-section 400 of an exemplary AlGaIn/GaN Schottky metal-2DEG TJ-FET fabrication including formation of a recessed source and a Schottky source contact 110.

As a non-limiting example, in forming the recessed source and Schottky source contact, dry etching techniques such as ICP-RIE or other etching techniques that create low-damage and nearly vertical sidewall profile can be performed to etch through the Ill-nitride semiconductor barrier layer 106 and define the source contact region, recess, or groove. As a further example, the source recess or groove can be etched about 25 nm deep and can reach to the GaN layer (*e.g.*, Ill-nitride material buffer layer 104) so that the source metal is in direct contact to the sidewall of the 2DEG channel (*e.g.*, approximately 6 nm into the Ill-nitride material buffer layer 104) as measured from the top surface of the Ill-nitride material buffer layer 104).

Subsequently, a metal layer 110 (*e.g.*, Schottky source contact 110) with single or multiple metal layers (*e.g.*, Ti, Al, Cr, Ni, Pt, Au, *etc.*) can be deposited on Ill-nitride material buffer layer 104 to form a Schottky contact to 2DEG. For example, in a particular non-limiting implementation, metal layer 110 (*e.g.*, Schottky source contact 110) can be formed in the recess or groove by depositing single or multiple metal layers comprising one or more of Ti and Au. It should be noted that, according to various embodiments, the tunnel junction exists at the metal-2DEG junction.

According to further non-limiting methodologies 3500, a gate insulating dielectric layer can be deposited on the developing TJ-FET at 3510. In a non-limiting example, FIG. 5 further illustrates a schematic cross-section 500 of the AlGaIn/GaN metal-2DEG TJ-FET after depositing gate insulating dielectric layer 112. According to various embodiments, gate insulating dielectric layer 112 or passivation layer can comprise a dielectric (*e.g.*, Al_2O_3 , AlN, SiN, SiO_2 , HfO_2 , *etc.*) that can be grown or deposited on Ill-nitride semiconductor barrier layer 106. As a further example, in a particular non-limiting embodiment, a gate insulating dielectric layer 112 can comprise an Al_2O_3 layer (*e.g.*, a 10 nm Al_2O_3 layer grown, for example, by ALD). In addition, in further exemplary implementations, wet etching such as a buffered oxide etch (BOE) or dry etch techniques can be performed to etch through gate insulating

dielectric layer 112 to expose source (*e.g.*, Schottky source contact 110 region) and drain contact (*e.g.*, ohmic contact layer 108 region) regions.

In addition, methodologies 3500 can further include depositing a gate on gate insulating dielectric layer at 3512. For instance, FIG. 6 depicts a schematic cross-section of an exemplary AlGaIn/GaN metal-2DEG TJ-FET 600 after the formation of a gate electrode 602 and interconnects on the source contact 604 (*e.g.*, Schottky source contact 110 region) and drain contact 606 (*e.g.*, ohmic contact layer 108 region) regions. As can be seen in FIG. 6, a gate metallization layer 114 can be formed by single or multiple metal layers (*e.g.*, including Al, Ti, Ni, Pt, Au, TiN, TiW, *etc.*).

According to an aspect, gate metallization layer 114 can be deposited on gate insulating dielectric layer 112, and can be further deposited on source (*e.g.*, Schottky source contact 110 region) and drain contact (*e.g.*, ohmic contact layer 108 region) regions to form source and drain interconnects as shown in FIG. 6. As a further example, in a particular non-limiting embodiment, gate electrode 602 and source 604 (*e.g.*, Schottky source contact 110 region) can overlap (*e.g.*, overlap by 0.25 μm). Note further, however, that gate electrode 602 and source 604 are electrically separated by the gate insulating dielectric layer 112. In yet other exemplary implementations, AlGaIn/GaN metal-2DEG TJ-FET can include passivation layer 116 which shall be formed with insulating dielectric materials such as SiN, SiO₂, Al₂O₃, polyimide, *etc.*

While the disclosed subject matter has been described in connection with the preferred embodiments of the various figures, it is to be understood that other similar embodiments may be used or modifications and additions may be made to the described embodiments for performing the same function of the disclosed subject matter without deviating therefrom. For example, one skilled in the art will recognize that aspects of the disclosed subject matter as described in the various embodiments of the present application may apply to other Group III-Nitride heterostructures, other insulating or semiconducting materials or substrates, *etc.*

For instance, in various embodiments, the disclosed subject matter applies to III-nitride metal-2DEG tunnel junction field-effect transistors (TJ-FETs). As described herein, exemplary non-limiting TJ-FETs can comprise a substrate layer (*e.g.*, Si, sapphire, SiC, GaN, AlN, *etc.*), a III-nitride nucleation layer above the substrate, a III-nitride undoped buffer layer above the nucleation layer, a III-nitride undoped channel layer above the buffer layer, and so on. Note that, the channel layer could be the same

as the Ill-nitride buffer layer (*e.g.*, GaN) or it could be different from the buffer layer (*e.g.*, when the buffer is selected as AlGa_N, the channel layer can be selected as GaN).

In addition, exemplary non-limiting TJ-FETs can include a Ill-nitride barrier layer including a cap layer, a two-dimensional electron gas (2DEG) conducting channel
5 located at the heterointerface between the buffer layer and the barrier layer, and a metallic source electrode making Schottky contact to the 2DEG channel.

In addition, in further implementations, exemplary non-limiting TJ-FETs can comprise a metallic drain electrode making ohmic contact to the 2DEG channel, and an insulating dielectric layer above the said barrier layer, which dielectric layer also
10 covers the source electrode, at least in part. Moreover, exemplary implementations can include a metallic gate electrode on top of the gate dielectric layer partially overlapping but electrically separated from (by the said gate dielectric layer) the source electrode, in addition to a final passivation layer made of dielectric materials.

As described above, various modifications are contemplated. For instance,
15 exemplary TJ-FETs can comprise a source region recessed into the channel layer and exposing the 2DEG channel along the sidewalls of the recessed region, for instance to enable the source Schottky contact to be in contact with the 2DEG along the exposed sidewall. In addition, disclosed TJ-FETs are capable of normally-off or enhancement-mode operation with positive threshold voltage by appropriate 2DEG density in as-grown epitaxial wafer. Disclosed TJ-FETs can also comprise a 2DEG channel having
20 high density that is in Schottky contact with the source metal in order to achieve thin tunnel barrier with high tunneling coefficient. As described above, Disclosed TJ-FETs are capable of delivering high ON/OFF current ratio and low off-state leakage due in part to the Schottky source providing a naturally reverse biased Schottky
25 junction that suppresses the buffer leakage.

In addition, disclosed TJ-FETs can also comprise an ohmic drain that can facilitate a device free of drain bias offset and that can deliver low on-resistance. Moreover, in an aspect the drain contact to the 2DEG channel can be made in the form of Schottky contact rather than an Ohmic contact to provide reverse drain
30 blocking capability. Advantageously, the disclosed subject matter can, in various embodiments, deliver small sub-threshold slope as the turn-on of the conducting channel is determined by the tunneling process instead of being limited by the diffusion process. Various implementations can also be immune to drain induced

barrier lowering effect, as described above, making it especially attractive for short-channel devices.

Note that, according to various embodiments, disclosed TJ-FETs can have higher off-state breakdown voltage than conventional HEMT as the depletion starts from the source tunnel junction instead the gate edge on the drain side. Additionally, various
5 embodiments can include source electrodes that are highly scalable and can be readily reduced in size. Thus, as a further advantage, various embodiments can be monolithically integrated with conventional depletion-mode HEMT and/or MIS-HEMT (metal-insulator-semiconductor HEMT) fabricated on the same wafer, which
10 can be used to realize directly coupled FET logic circuits, III-nitride smart power integrated circuits that feature complete integration of power devices and digital/analog functional blocks, *etc.*

As described above, for certain embodiments, current flow can be said to flow in a lateral path from the source to the drain, resulting in a lateral device. Where current
15 flow can be said to flow in a vertical path from the source to the drain, and across the heterojunction, the devices are described as vertical devices.

For instance, an exemplary non-limiting device implemented in a vertical structure can comprise one or more of a substrate layer (*e.g.*, Si, sapphire, SiC, GaN, AlN, *etc.*), a III-nitride nucleation layer above the substrate, a heavily-doped (*e.g.*,
20 with Si as the dopant) n-type III-nitride semiconductor contact layer above the nucleation layer, a lightly-doped III-nitride semiconductor spacer layer above the heavily-doped n-type contact layer, an undoped III-nitride semiconductor channel layer above the lightly-doped III-nitride spacer layer, a III-nitride barrier layer including a cap layer and a two-dimensional electron gas (2DEG) conducting channel
25 located at heterointerface between the channel layer and the barrier layer. In addition, exemplary implementations can include a metallic source electrode making Schottky contact to the 2DEG channel, a metallic drain electrode making ohmic contact to the heavily doped contact layer, and an insulating dielectric layer above the barrier layer, where the dielectric layer also covers the source electrode.

30 In various implementations, a metallic gate electrode can be deposited on top of the gate dielectric layer and partially overlapping but electrically separated from (by the said gate dielectric layer) the source electrode. In addition, according to further exemplary implementations, the gate electrode can be located in a trench that is etched to the channel layer, or the said spacer layer. As described above for lateral

devices, vertical devices can also be monolithically integrated with conventional HEMT and MIS-HEMT on the same wafer.

As a further example, in addition to the disclosed layers, it is conceivable that other layers for purposes other than described in one or more embodiments herein can be introduced between such layers. However, in such cases, such intermediate layers, without effect, can be considered as part of the disclosed layers. Moreover, sometimes layers inadvertently introduced (*e.g.*, process contaminants, oxidation, natural impurities, *etc.*) are also formed as a byproduct of an industrial fabrication process and such layers also are not to be considered separate layers.

In other instances, variations of process parameters (*e.g.*, dimensions, configuration, concentrations, concentration profiles, implant energies and doses, process step timing and order, addition and/or deletion of process steps, addition of preprocessing and/or post-processing steps, *etc.*) may be made to further optimize the provided structures, devices and methodologies, as shown and described herein. In any event, the structures and devices, as well as the associated methodologies described herein have many applications in tunnel-junction field-effect transistors. Therefore, the disclosed subject matter should not be limited to any single embodiment described herein, but rather should be construed in breadth and scope in accordance with the appended claims.

CLAIMS

What is claimed is:

1. A tunnel-junction field-effect transistor (TJ-FET) having prospective locations
5 for a source, a gate, and a drain, the TJ-FET comprising:
a substrate comprising a buffer layer deposited on the substrate and a barrier layer deposited on the buffer layer, the buffer layer and the barrier layer forming a heterojunction at an interface of the buffer layer and the barrier layer; and
a metal region adjacent to the buffer layer, proximate to the prospective
10 location for the source, and spanning a portion of the heterojunction.
2. The TJ-FET of claim 1, the substrate comprising at least one of sapphire, silicon (111), silicon carbide (SiC), aluminum nitride (AlN), or GaN.
- 15 3. The TJ-FET of claim 1, the buffer layer is deposited on the substrate over a nucleation layer comprised of a group III-nitride.
4. The TJ-FET of claim 1, the substrate comprises sapphire, the buffer layer comprises undoped GaN, and the barrier layer comprises a III-nitride barrier layer.
20
5. The TJ-FET of claim 1, further comprising:
an insulating dielectric layer deposited above the barrier layer proximate to the prospective location for the gate.
- 25 6. The TJ-FET of claim 5, further comprising:
the gate deposited above the insulating dielectric layer.
7. The TJ-FET of claim 6, the gate further adapted to partially overlay a portion of the metal region proximate to the prospective location for the source and
30 electrically isolated from the metal region by the insulating dielectric layer.
8. The TJ-FET of claim 7, the gate further adapted to at least partially fill a trench etched in a portion of the barrier layer.

9. The TJ-FET of claim 1, the heterojunction comprising a two-dimensional electron gas (2DEG) conducting channel proximate to the prospective location for the gate and in Schottky contact with the metal region proximate to the prospective location for the source.

5

10. The TJ-FET of claim 9, further comprising:
the drain spanning a portion of the heterojunction and in at least one of ohmic contact or Schottky contact with the 2DEG.

10 11. A normally-off metal two-dimensional electron gas (metal-2DEG) tunnel-junction field-effect transistor (TJ-FET), comprising:
a second nitride semiconductor layer deposited on a first nitride semiconductor layer;
a nitride semiconductor barrier layer deposited on the second nitride
15 semiconductor layer and forming a heterojunction comprising a two-dimensional electron gas (2DEG) at an interface of the nitride semiconductor barrier layer and the second nitride semiconductor layer; and
at least one metallic source contact associated with the metal-2DEG TJ-FET and in Schottky contact with the 2DEG.

20

12. The metal-2DEG TJ-FET of claim 11, further comprising at least one of an ohmic or a Schottky drain contact electrically coupled to the at least one metallic source contact across the heterojunction.

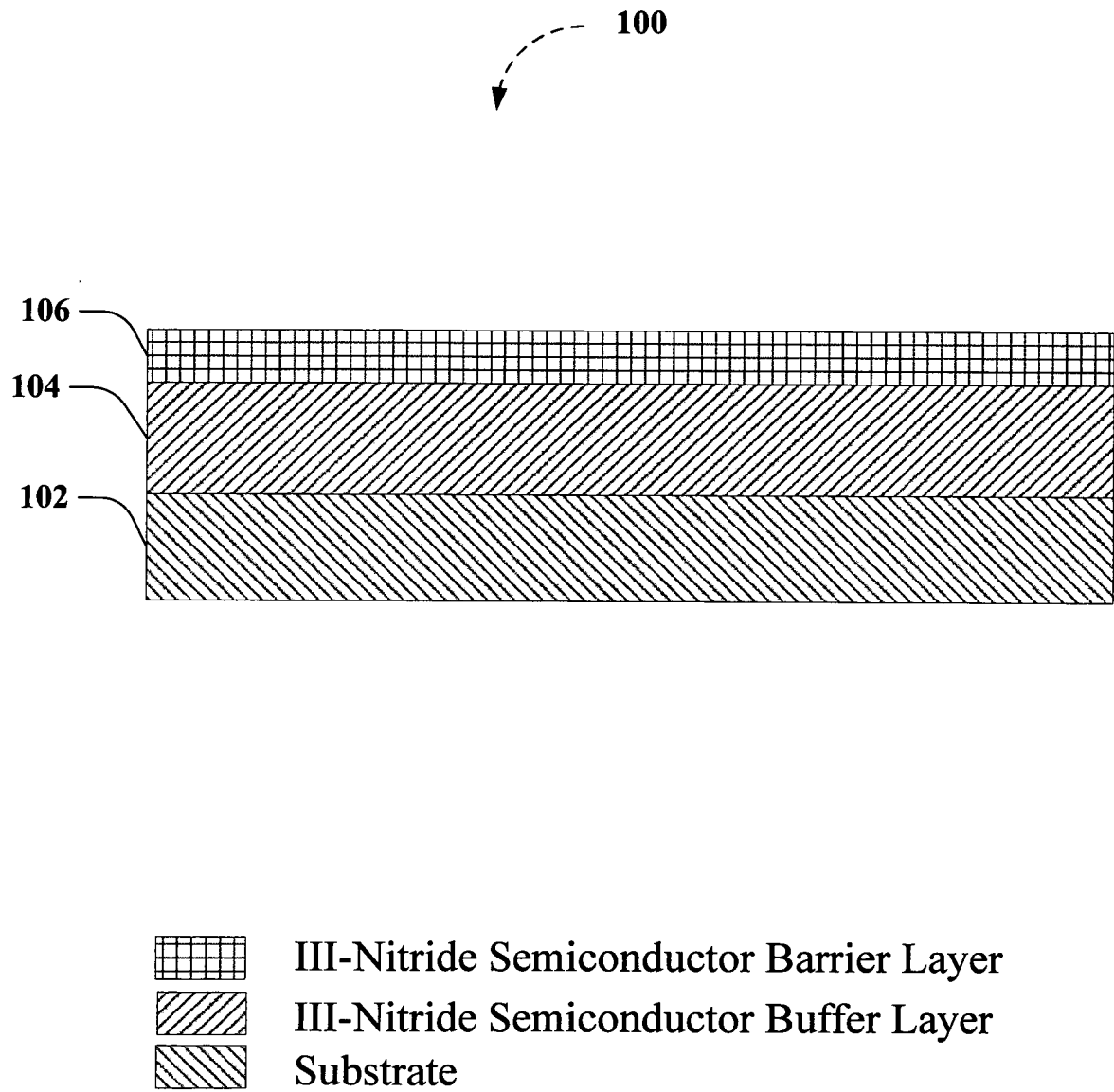
25 13. A method of forming a TJ-FET having at least one design location for a source, a gate, and a drain of the TJ-FET, the method comprising:
depositing a buffer layer over a substrate;
depositing a barrier layer over the buffer layer to form a heterojunction comprising a two-dimensional electron gas (2DEG); and
30 forming a metallic Schottky source contact to the 2DEG.

14. The method of claim 13, the depositing the buffer layer includes growing the buffer layer over at least one of a sapphire substrate, a silicon (111) substrate, a

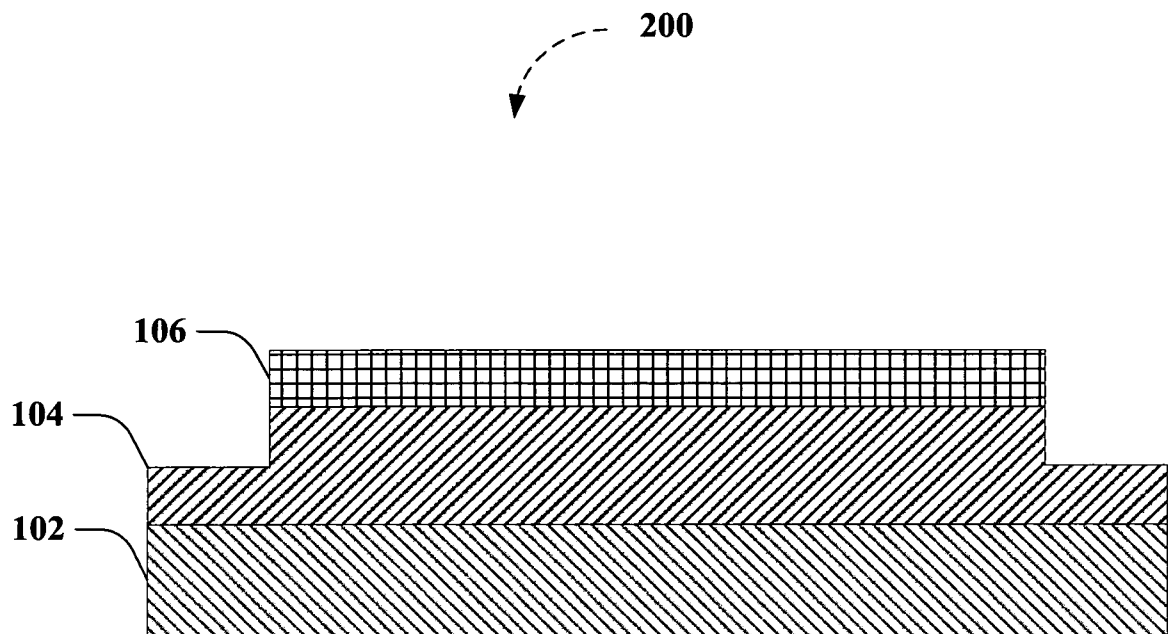
silicon carbide (SiC) substrate, an aluminum nitride (AlN) substrate, or a Gallium Nitride (GaN) substrate.

15. The method of claim 13, the depositing the buffer layer includes growing the
5 buffer layer over the substrate having a III-nitride nucleation layer.
16. The method of claim 13, further comprising:
trenching a portion of the barrier layer proximate to the design location for the
gate.
10
17. The method of claim 13, further comprising:
growing a gate insulating dielectric layer above the barrier layer proximate to
the design location for the gate.
- 15 18. The method of claim 17, further comprising:
forming a metallic gate over the gate insulating dielectric layer to partially
overlay a portion of the metallic Schottky source contact.
19. The method of claim 13, further comprising:
20 forming a drain contact in at least one of ohmic contact or Schottky contact
with the 2DEG.
20. The method of claim 19, the forming a drain contact includes electrically
coupling the drain contact to the metallic Schottky source contact across the
25 heterojunction.

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**FIG. 1**

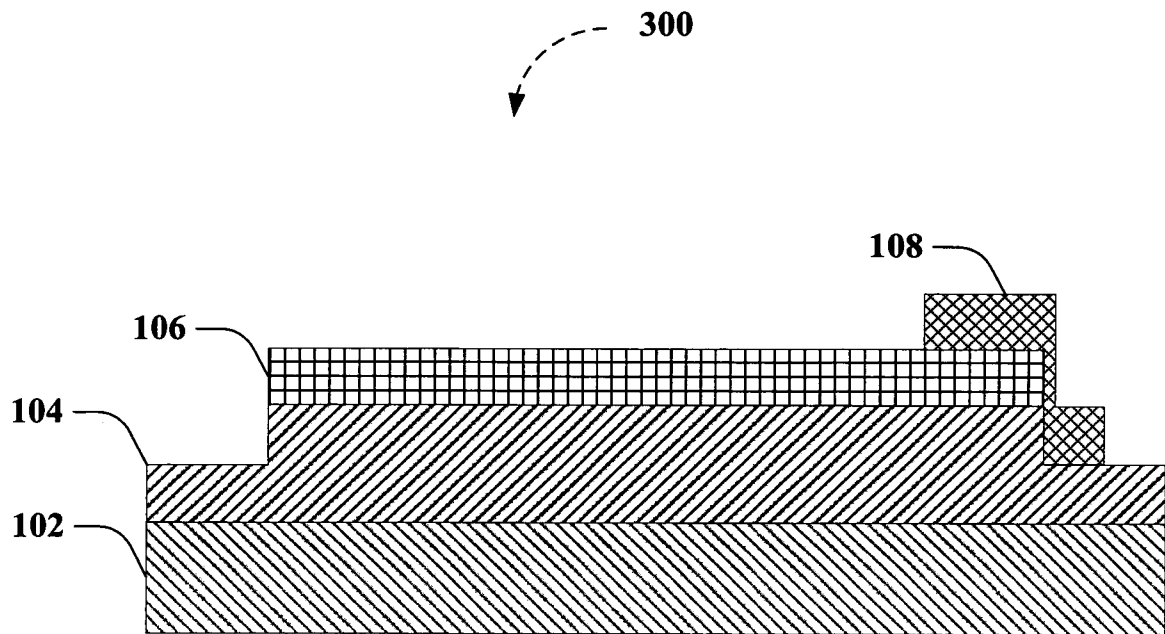
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- | | |
|---|---|
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

FIG. 2

3/35



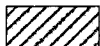
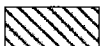
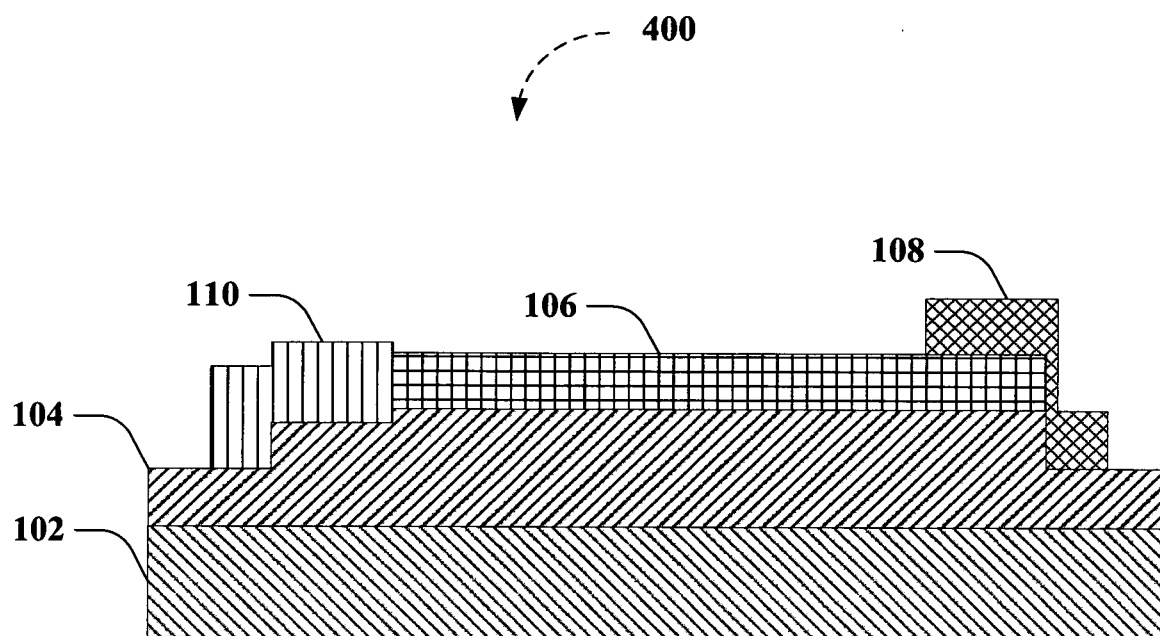
- | | |
|---|---|
|  | Ohmic Contact Layer |
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

FIG. 3

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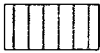
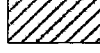
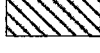
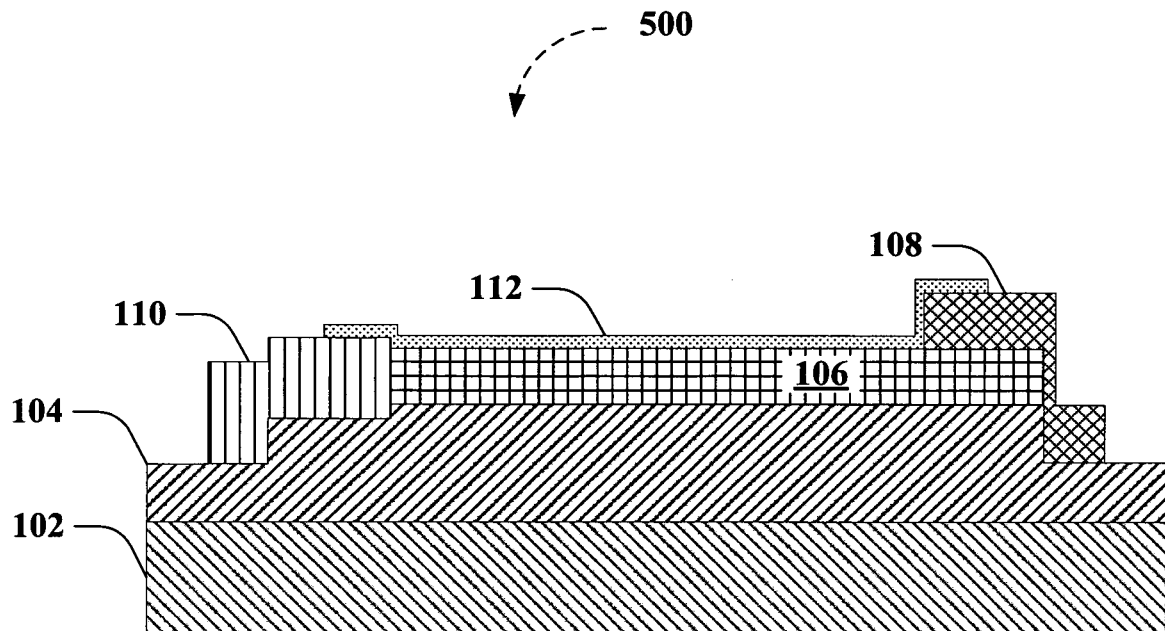
- | | |
|---|---|
|  | Metal Layer |
|  | Ohmic Contact Layer |
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

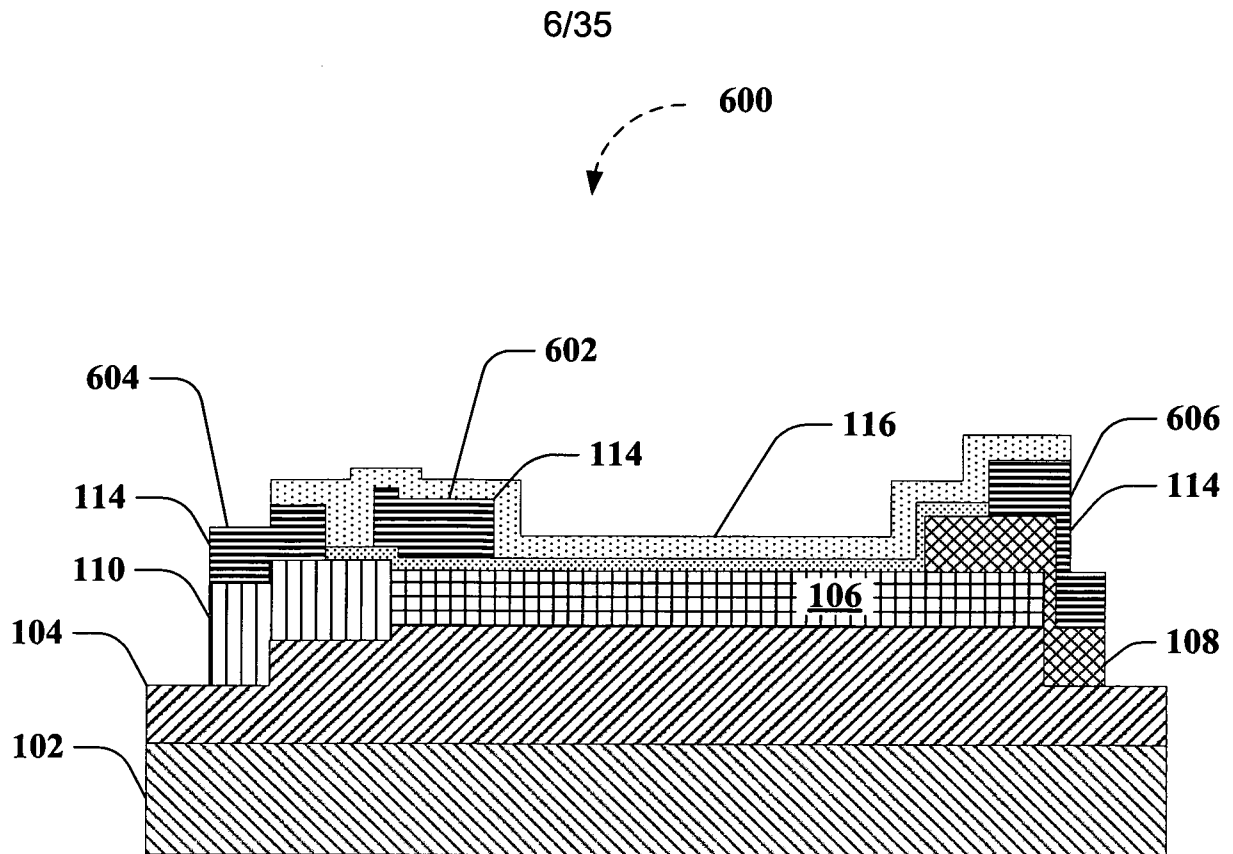
FIG. 4

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- | | |
|---|---|
|  | Gate Insulating Dielectric Layer |
|  | Metal Layer |
|  | Ohmic Contact Layer |
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

FIG. 5



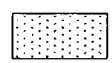
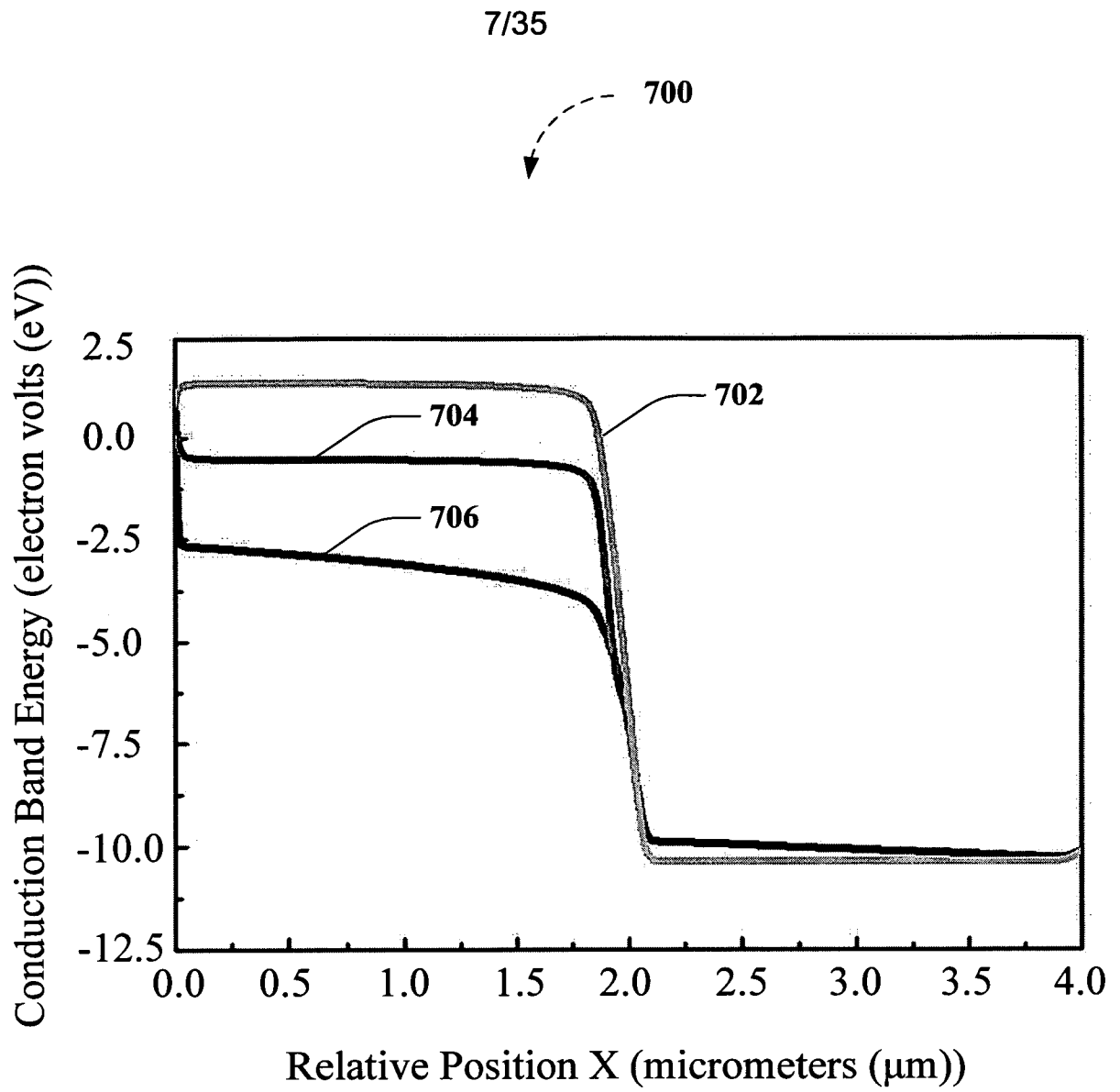
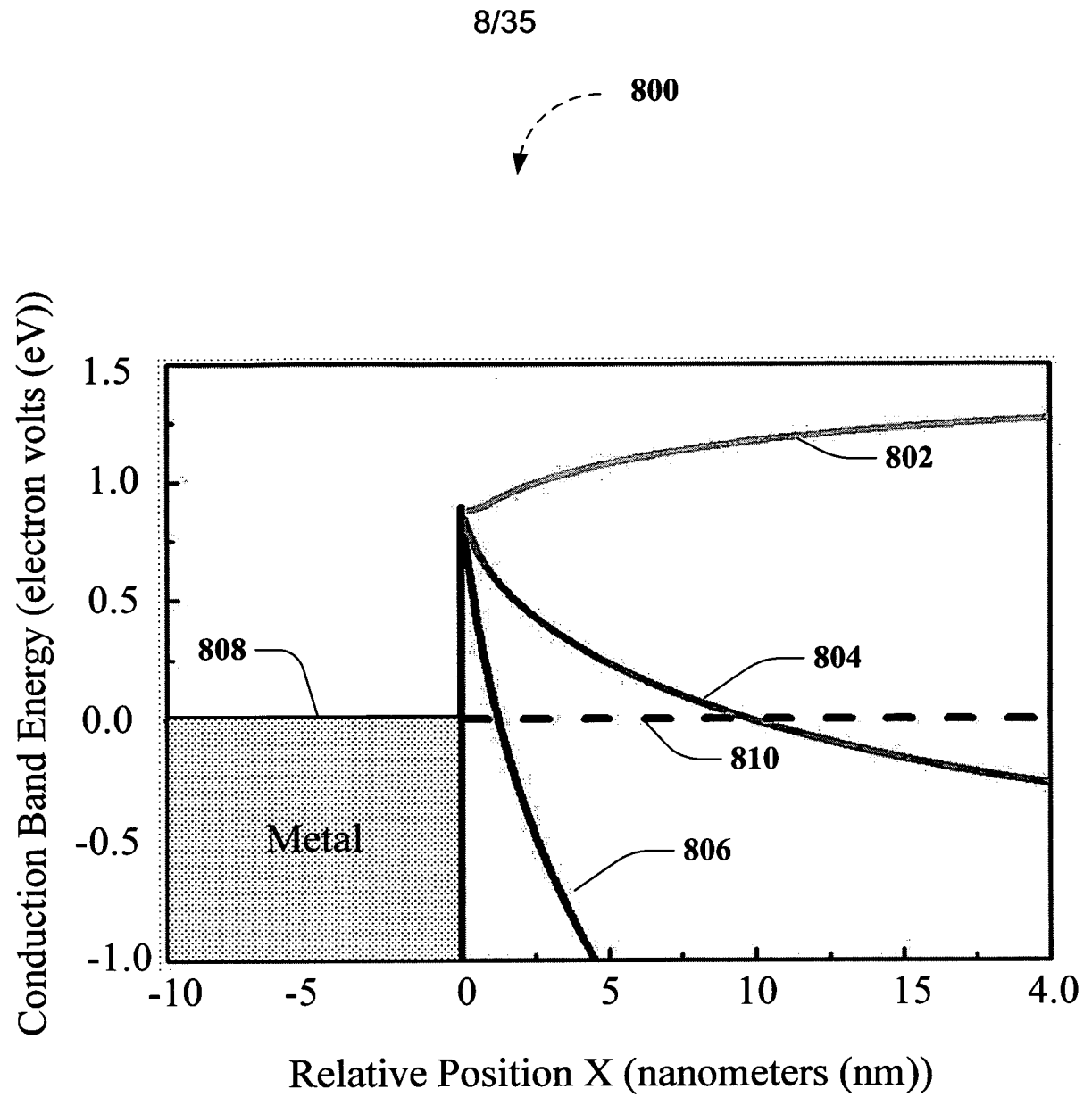
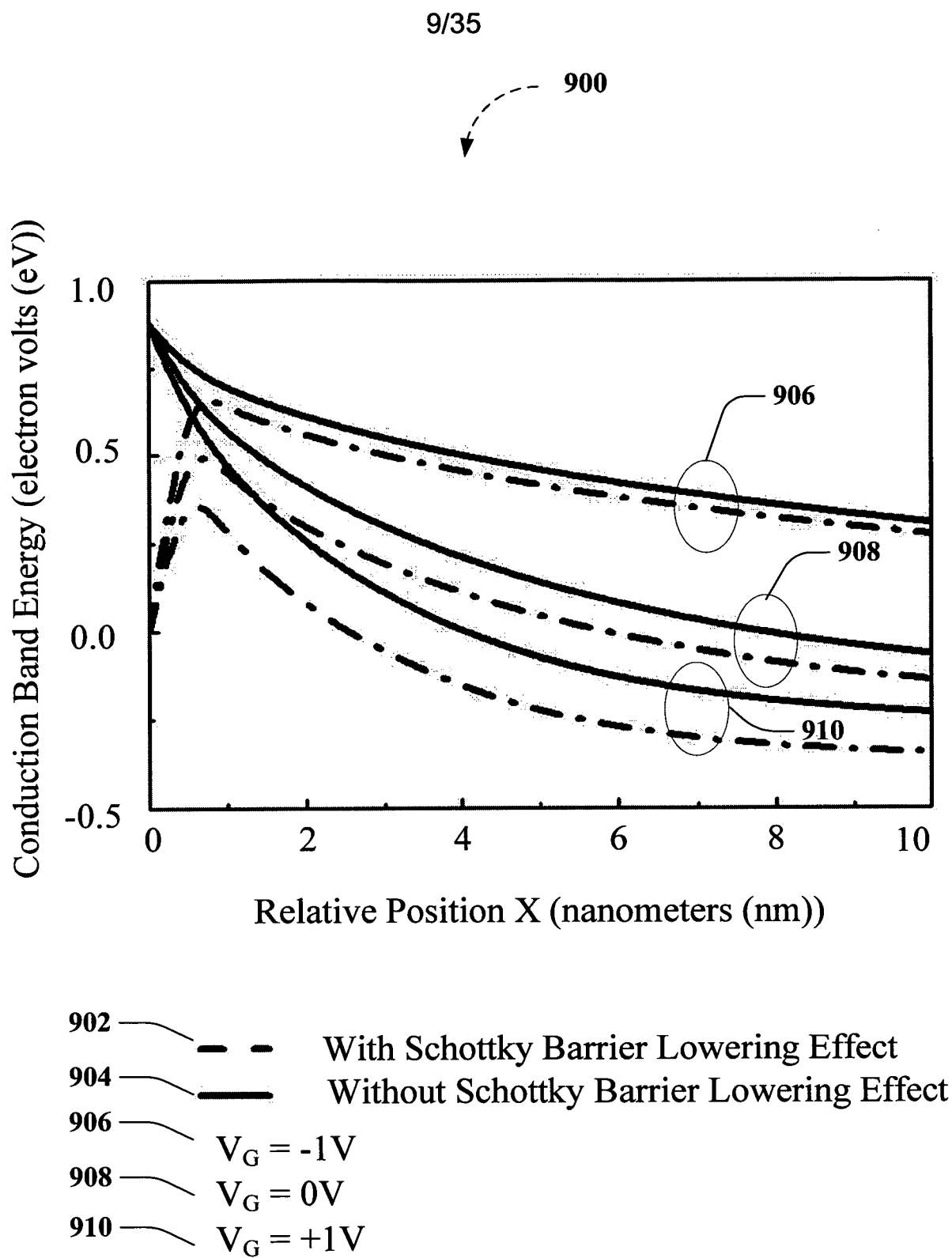
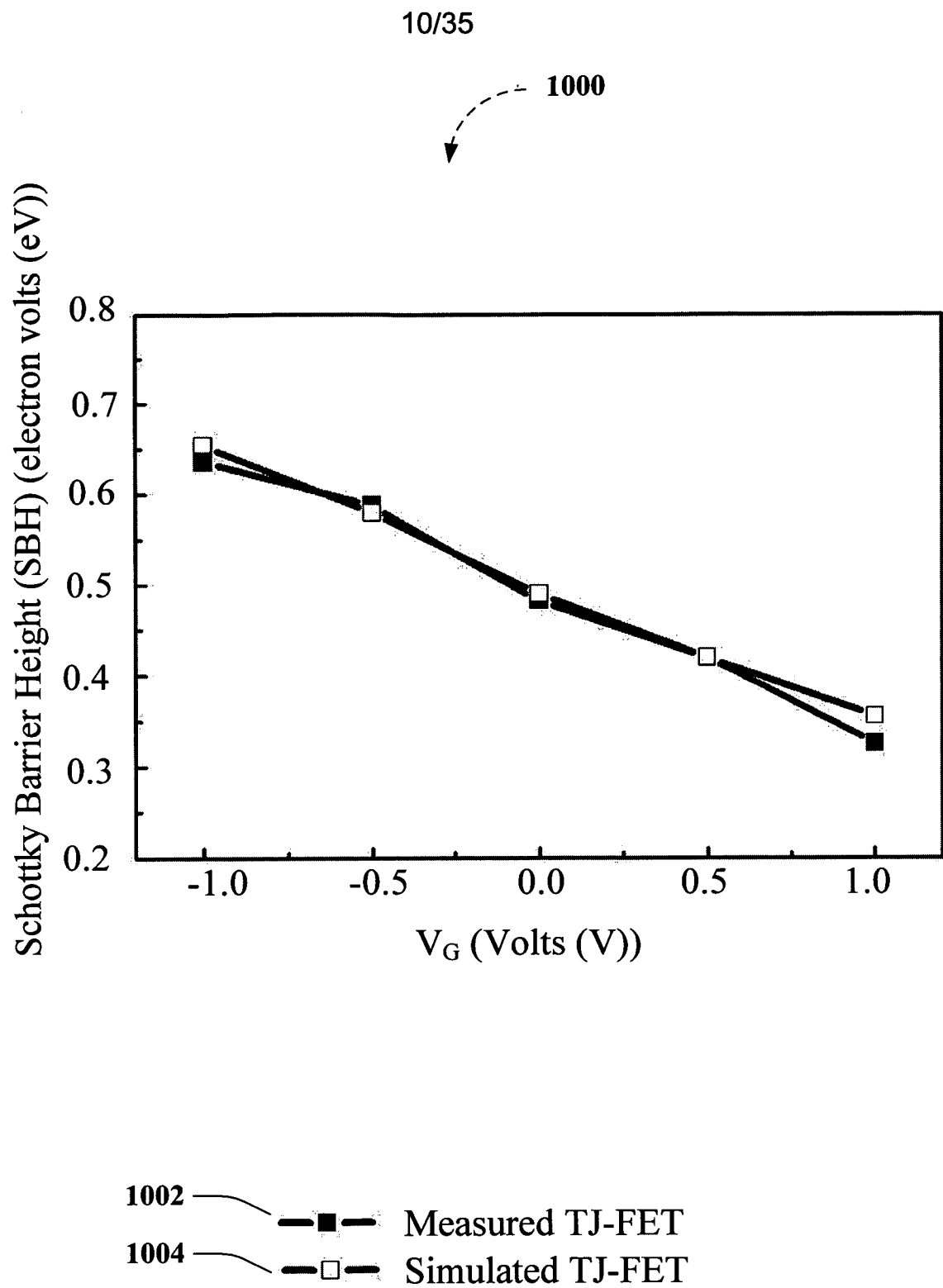
- | | |
|---|---|
|  | Passivation Layer |
|  | Gate Metallization Layer |
|  | Gate Insulating Dielectric Layer |
|  | Metal Layer |
|  | Ohmic Contact Layer |
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

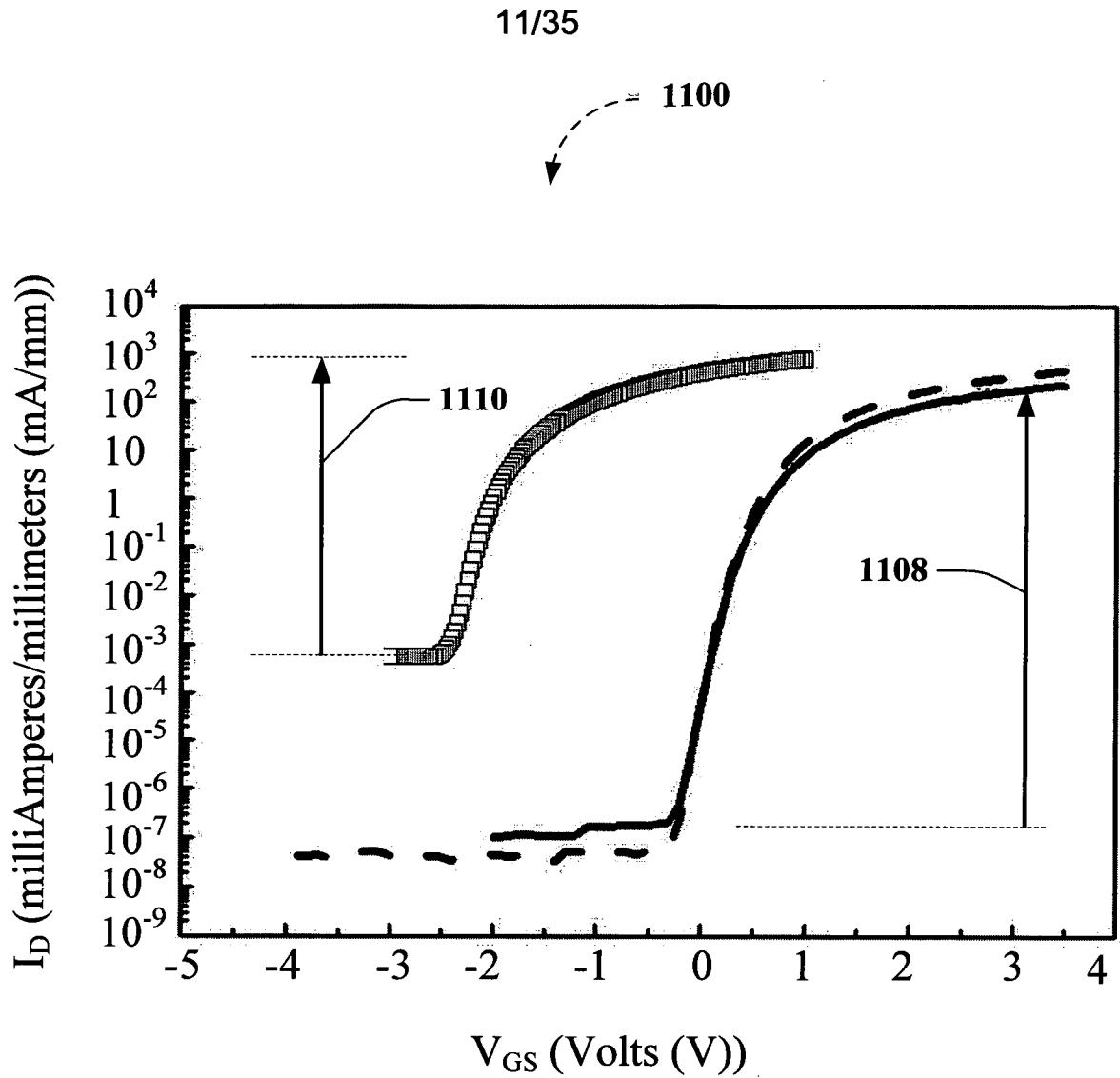
FIG. 6

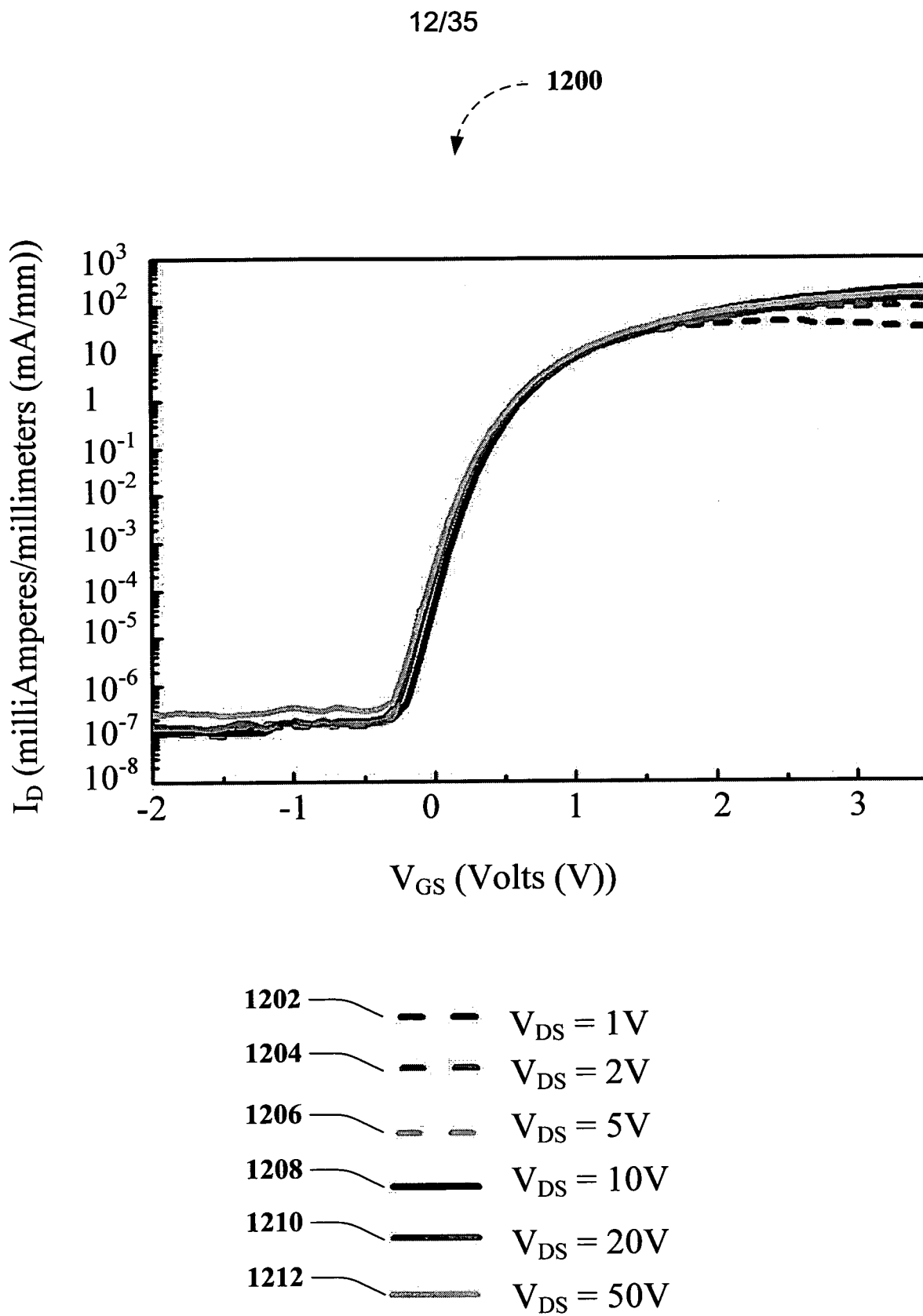
**FIG. 7**

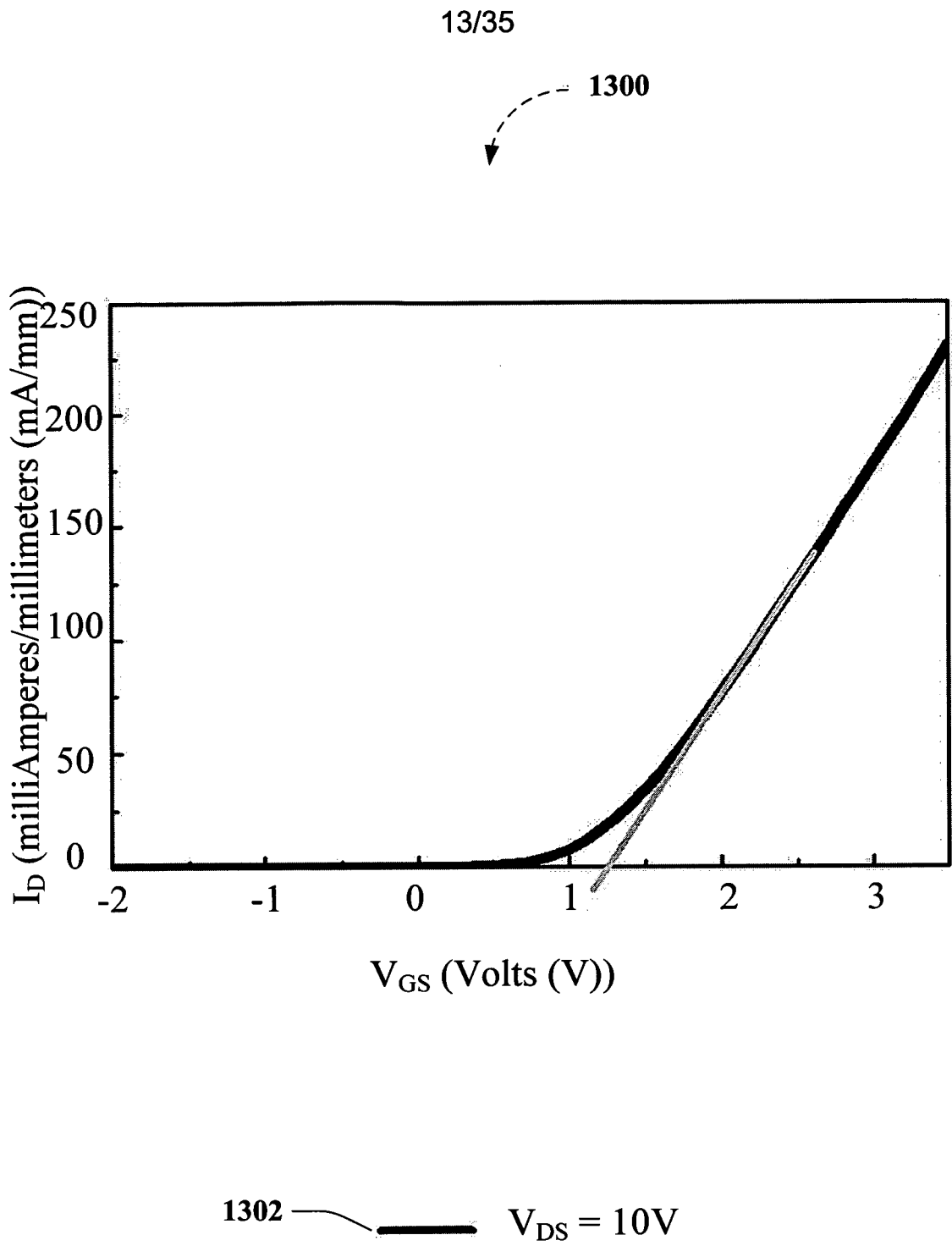
**FIG. 8**

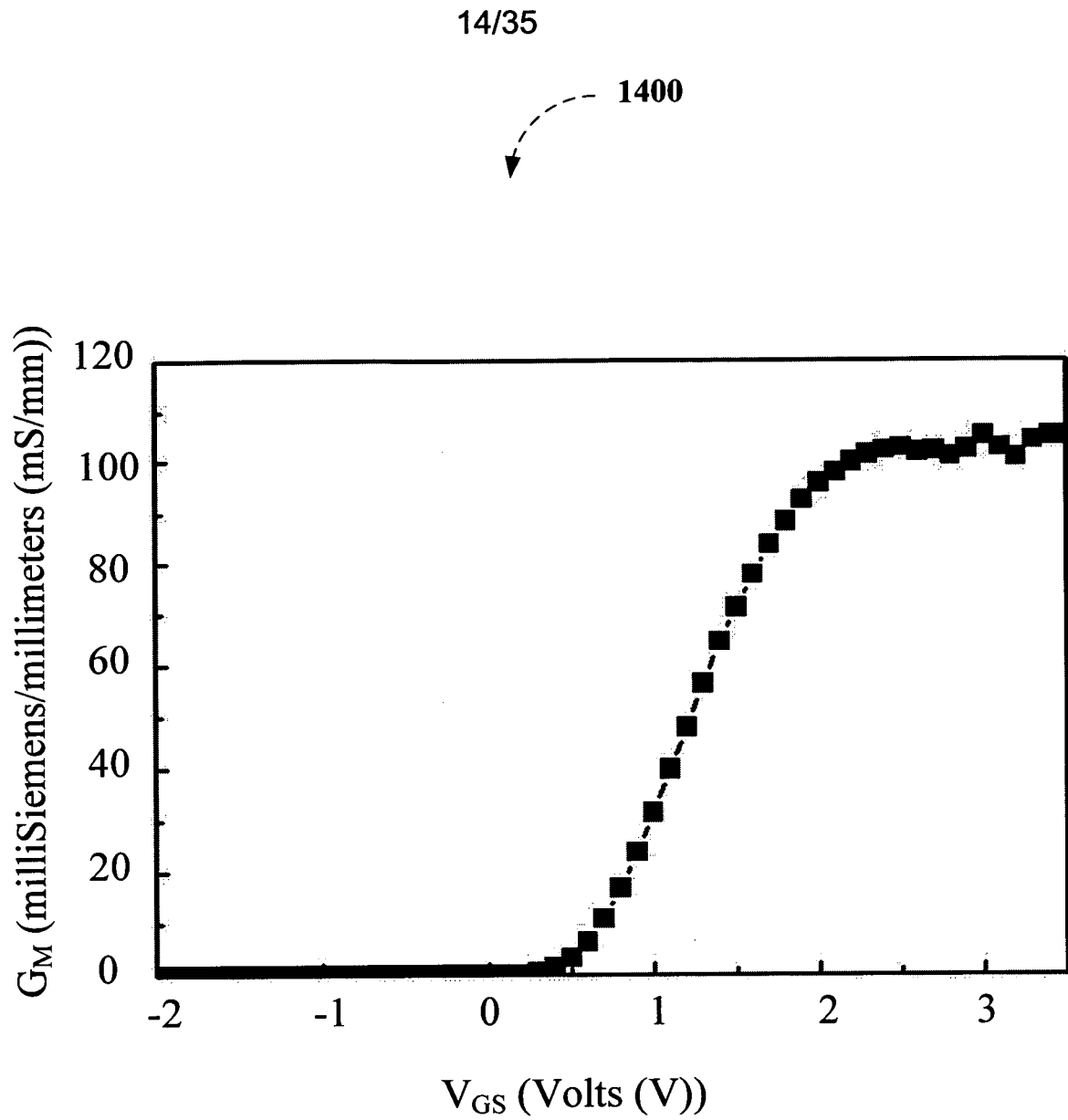
**FIG. 9**

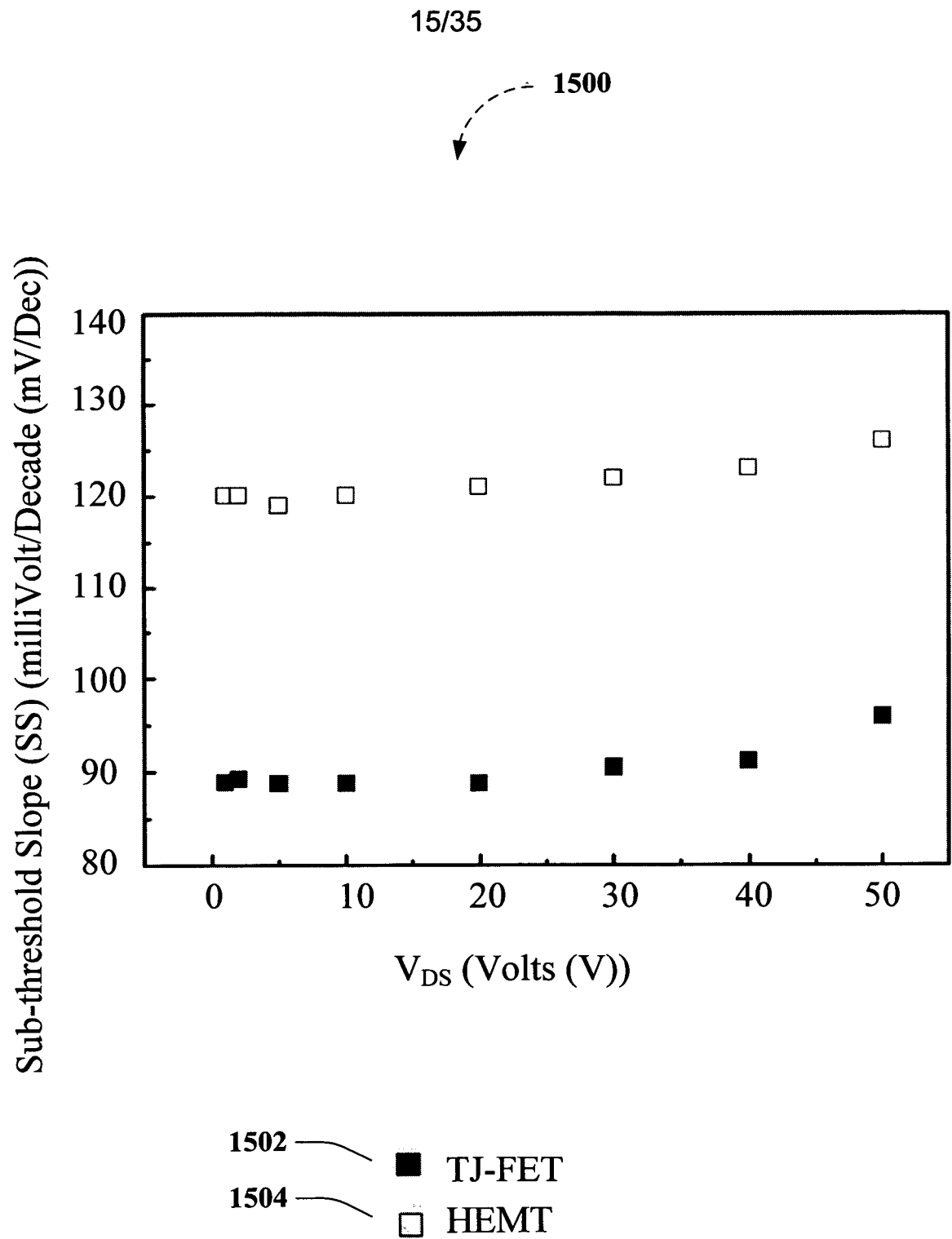
**FIG. 10**

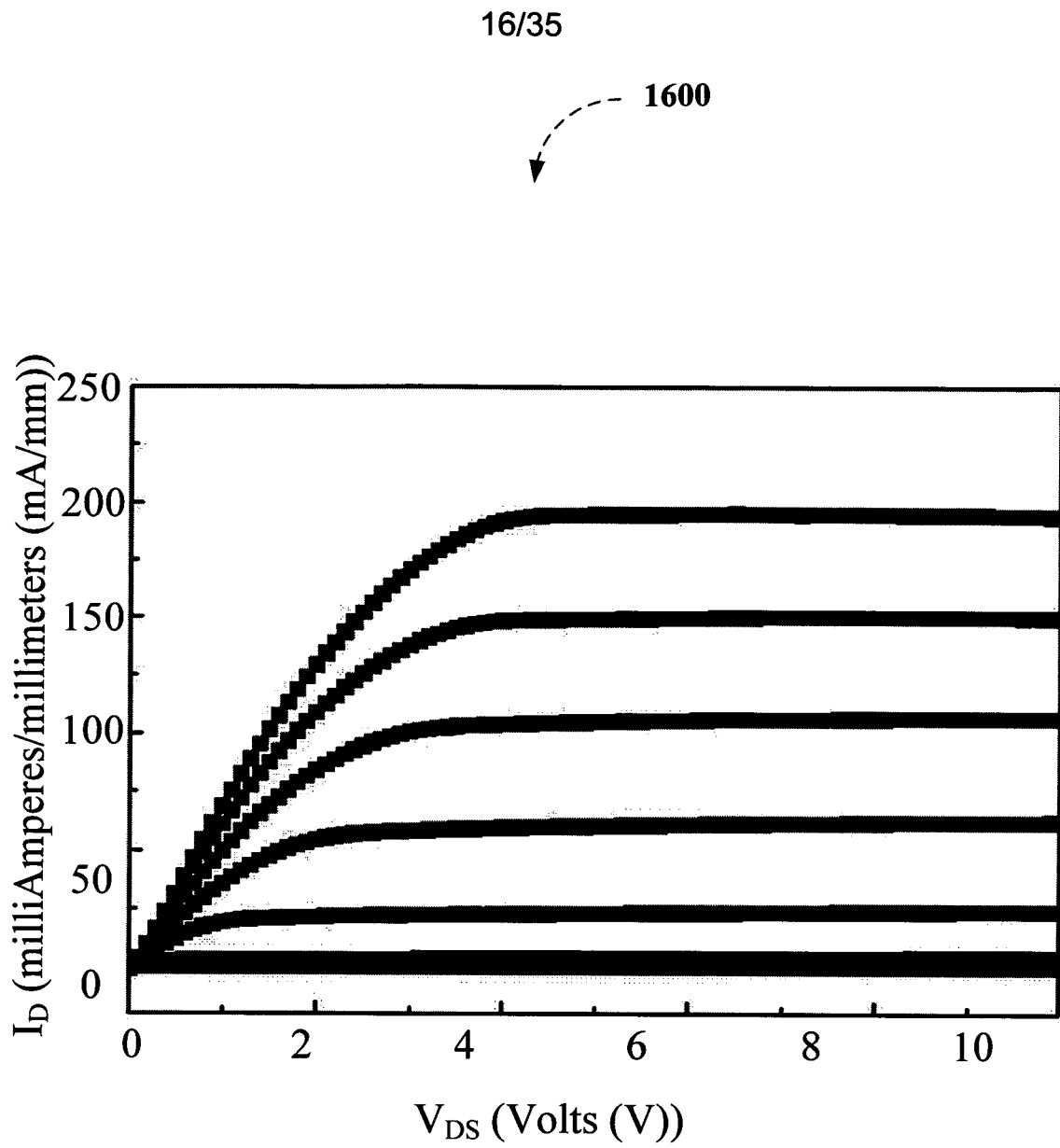
**FIG. 11**

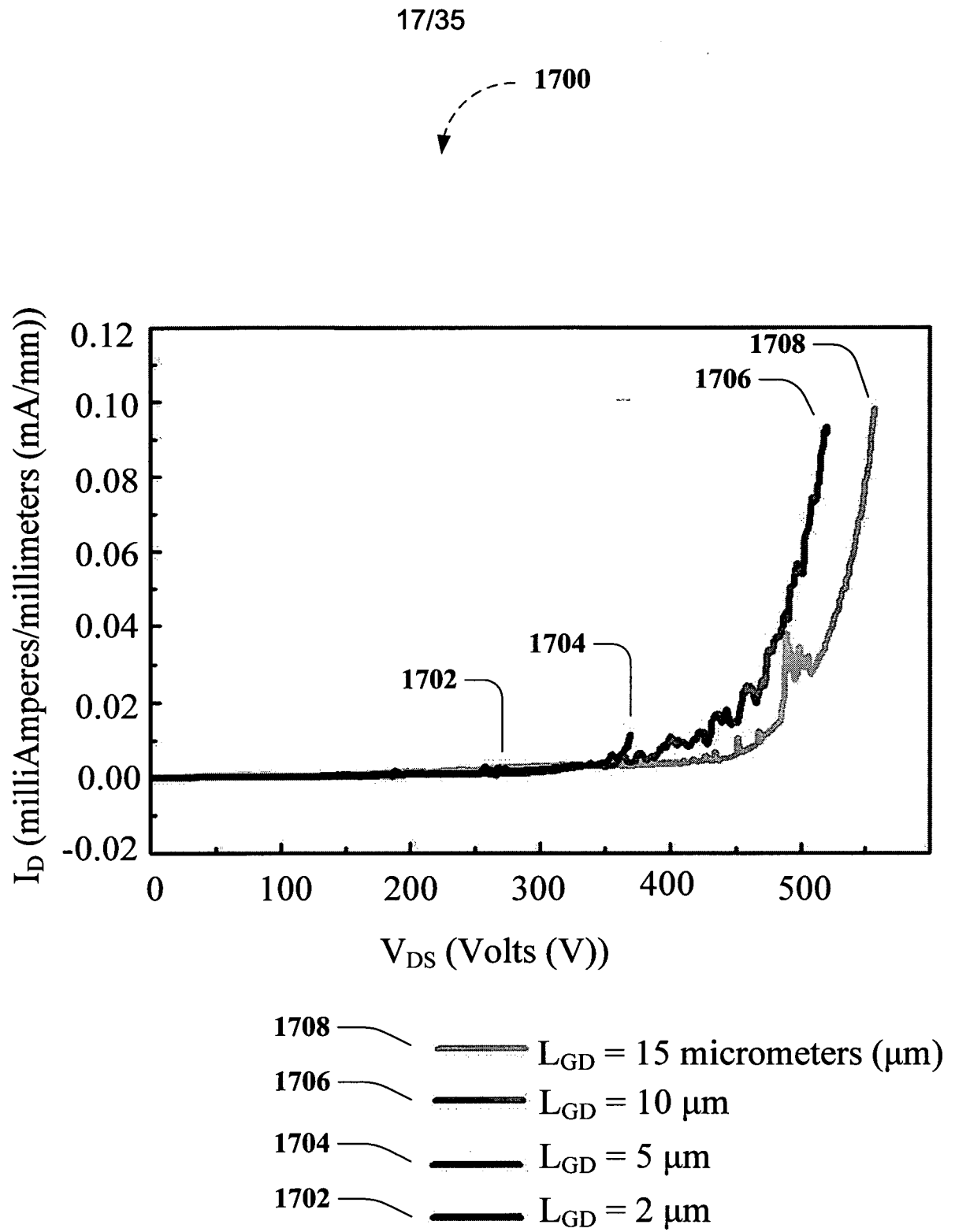
**FIG. 12**

**FIG. 13**

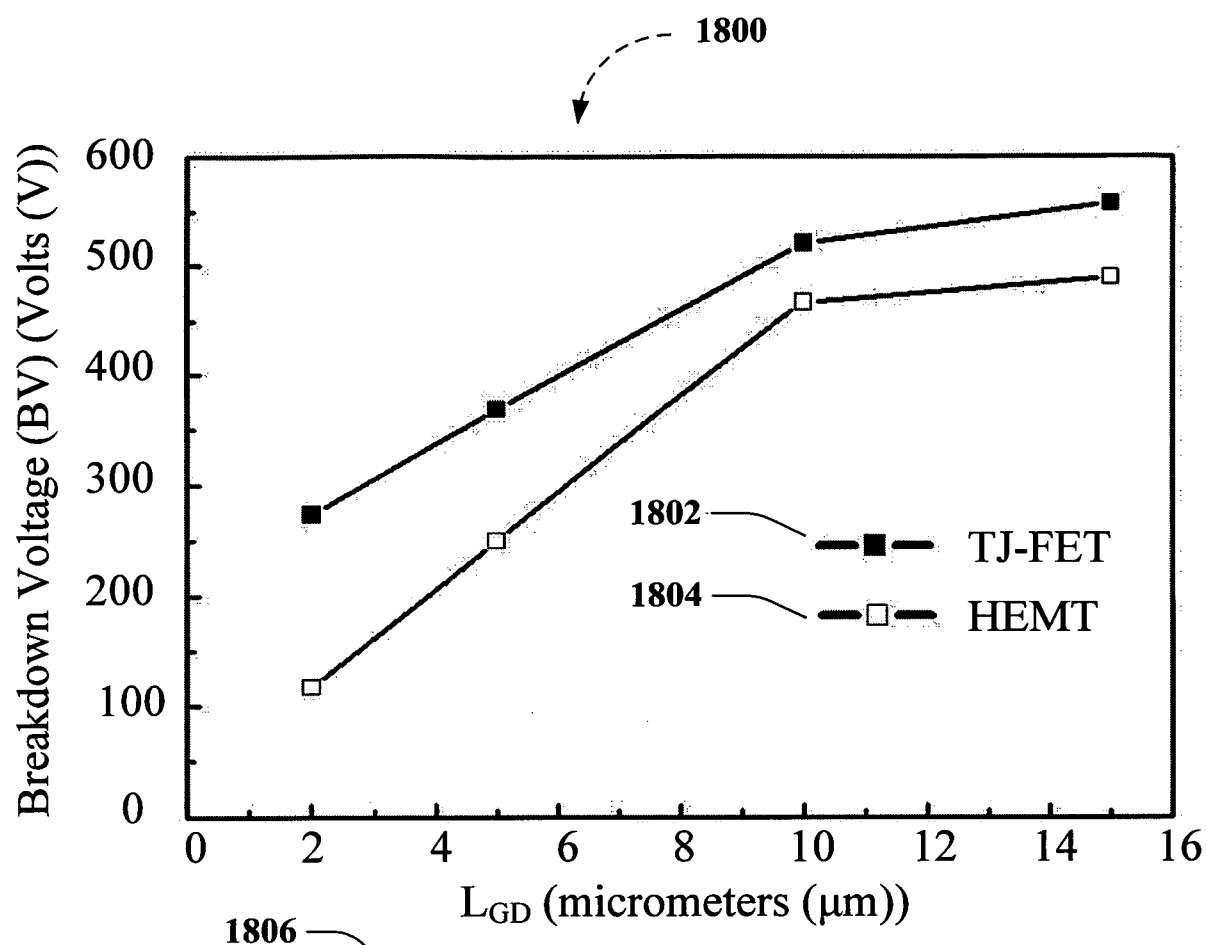
**FIG. 14**

**FIG. 15**

**FIG. 16**

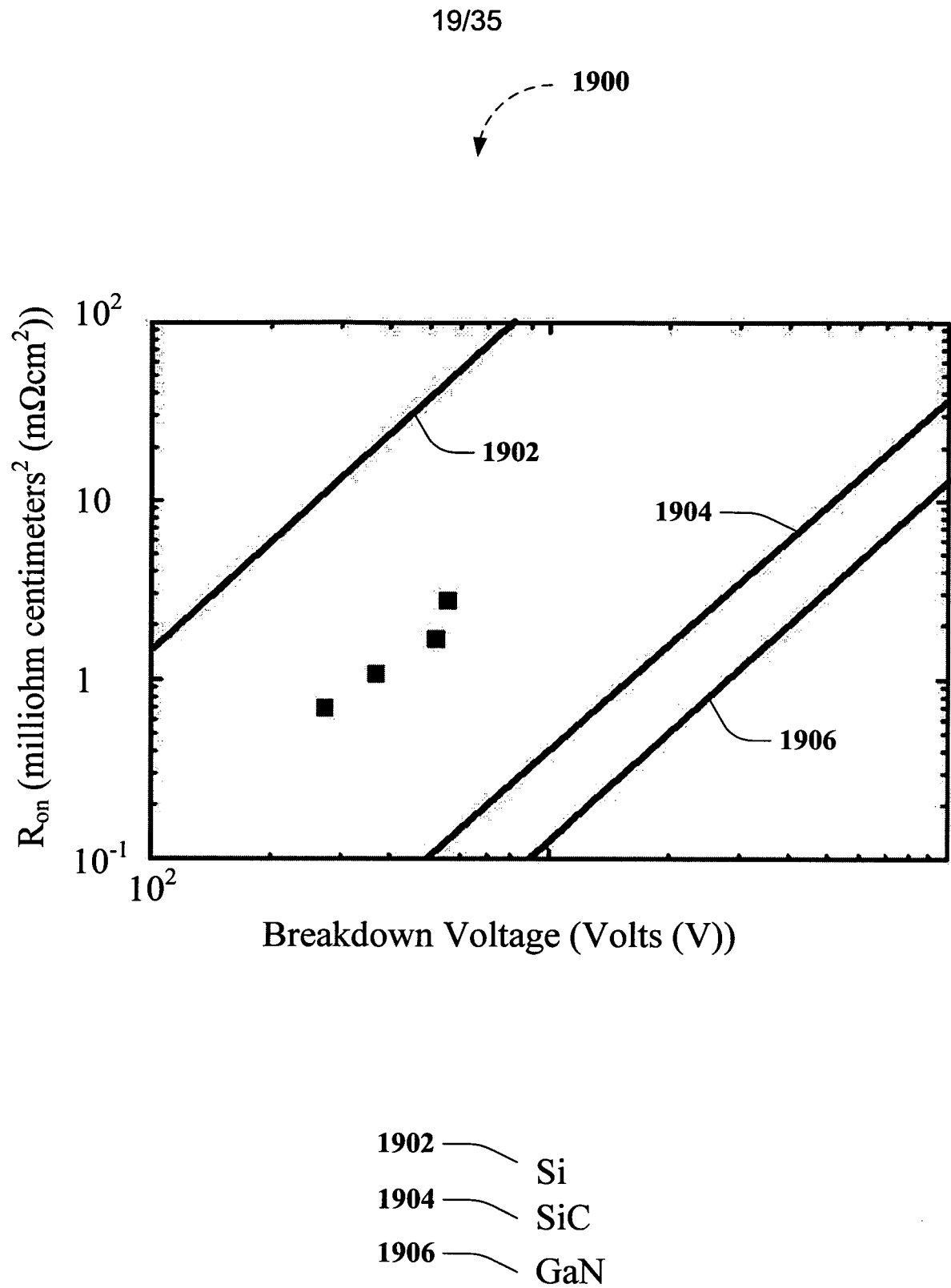
**FIG. 17**

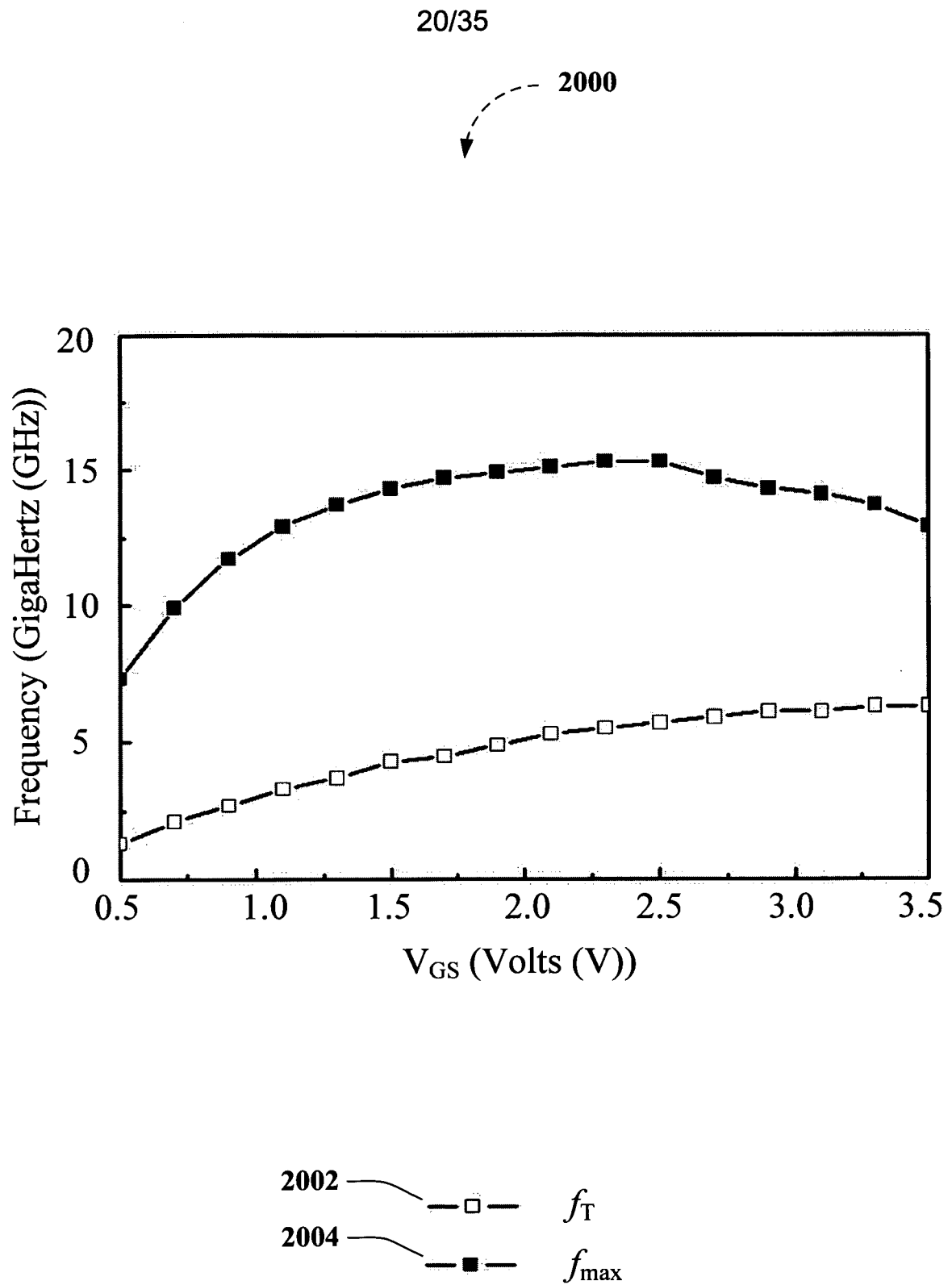
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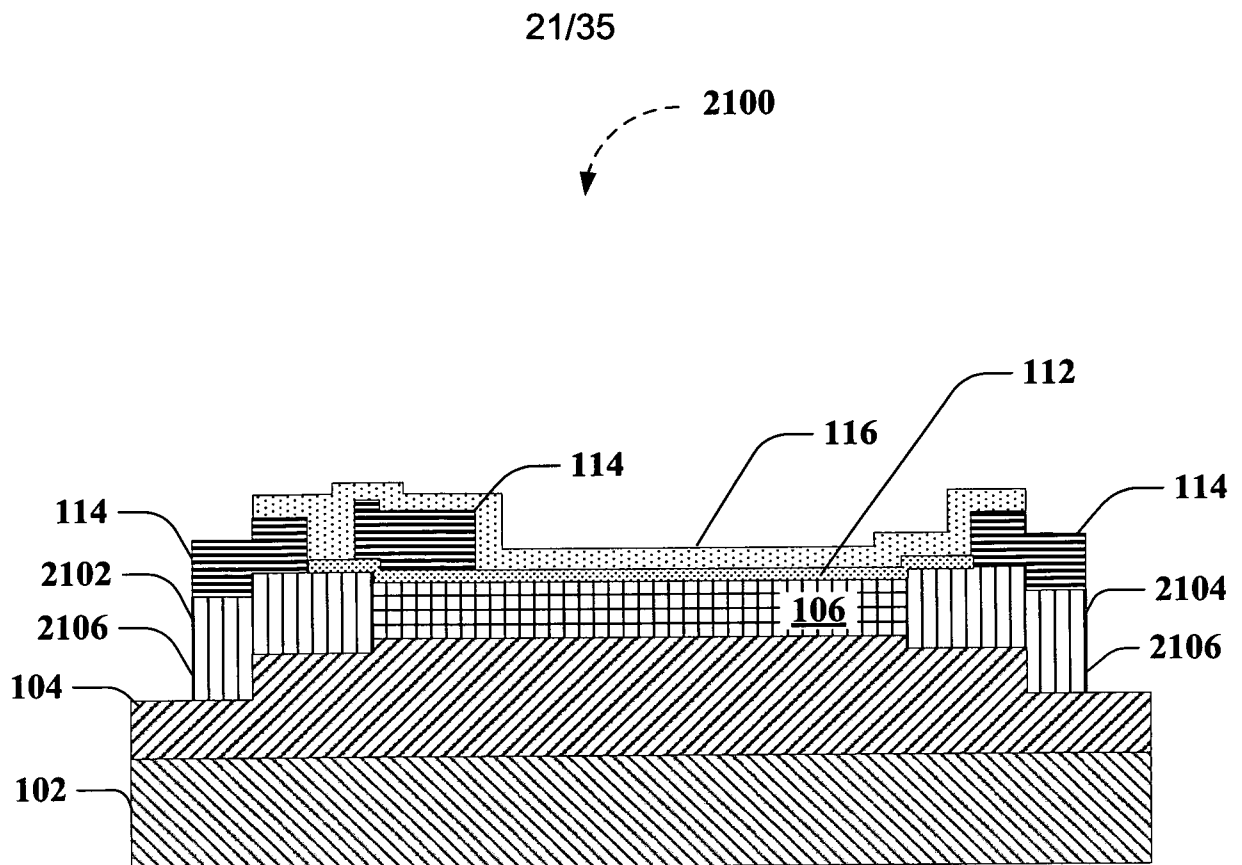


	TJ-FET	HEMT
I_{OFF} (mA/mm)	2×10^{-8}	6×10^{-4}
I_{ON} (mA/mm)	326	800
I_{ON}/I_{OFF}	10^{10}	10^6
SS (mV/Decade)	89	119
V_{th} (V)	+1.35	-2.1
BV (@0.1mA/mm) $L_{GD}=2\mu\text{m}$	274	117

FIG. 18

**FIG. 19**

**FIG. 20**



- | | |
|---|---|
|  | Passivation Layer |
|  | Gate Metallization Layer |
|  | Gate Insulating Dielectric Layer |
|  | Metal Layer |
|  | III-Nitride Semiconductor Barrier Layer |
|  | III-Nitride Semiconductor Buffer Layer |
|  | Substrate |

FIG. 21

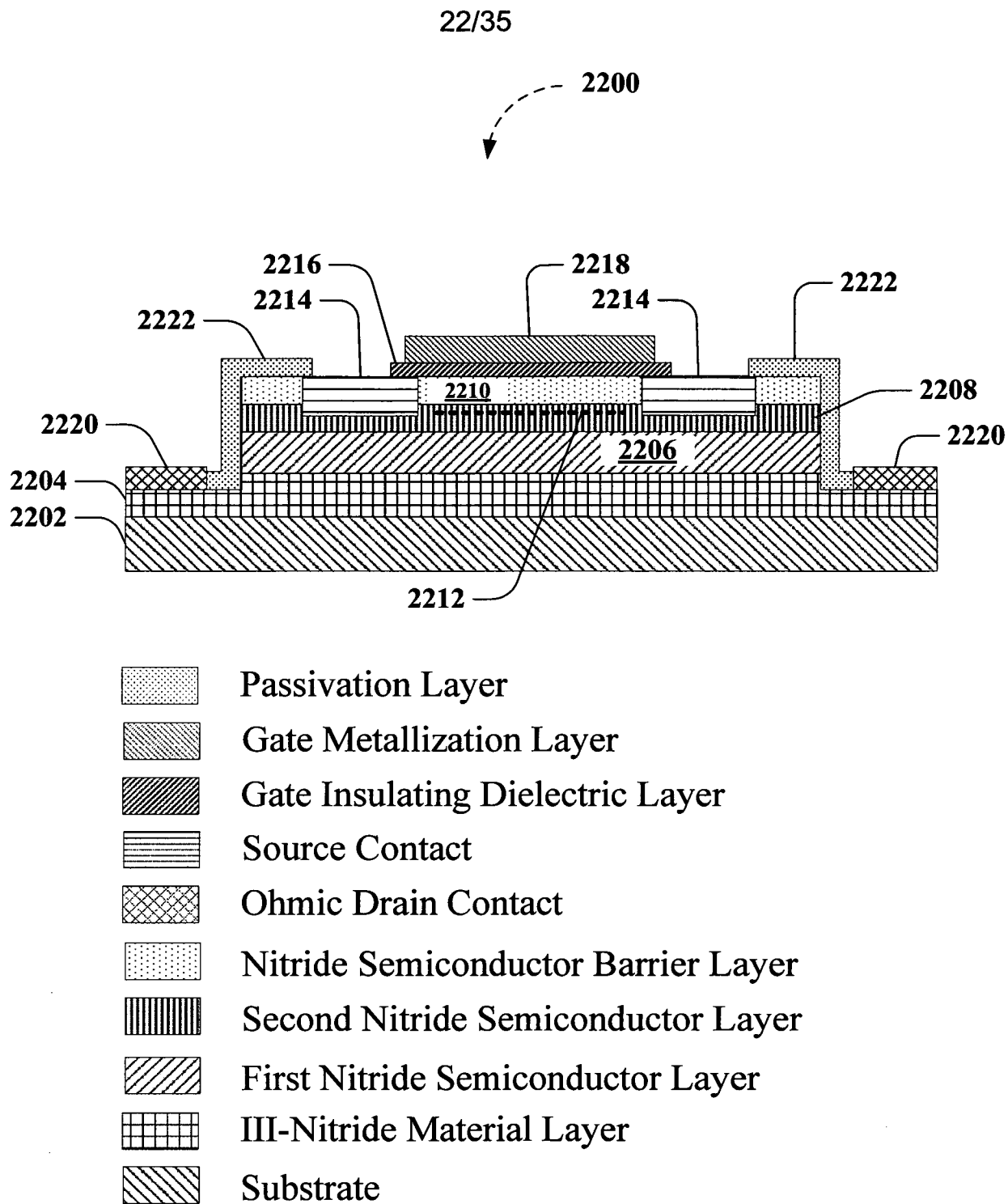
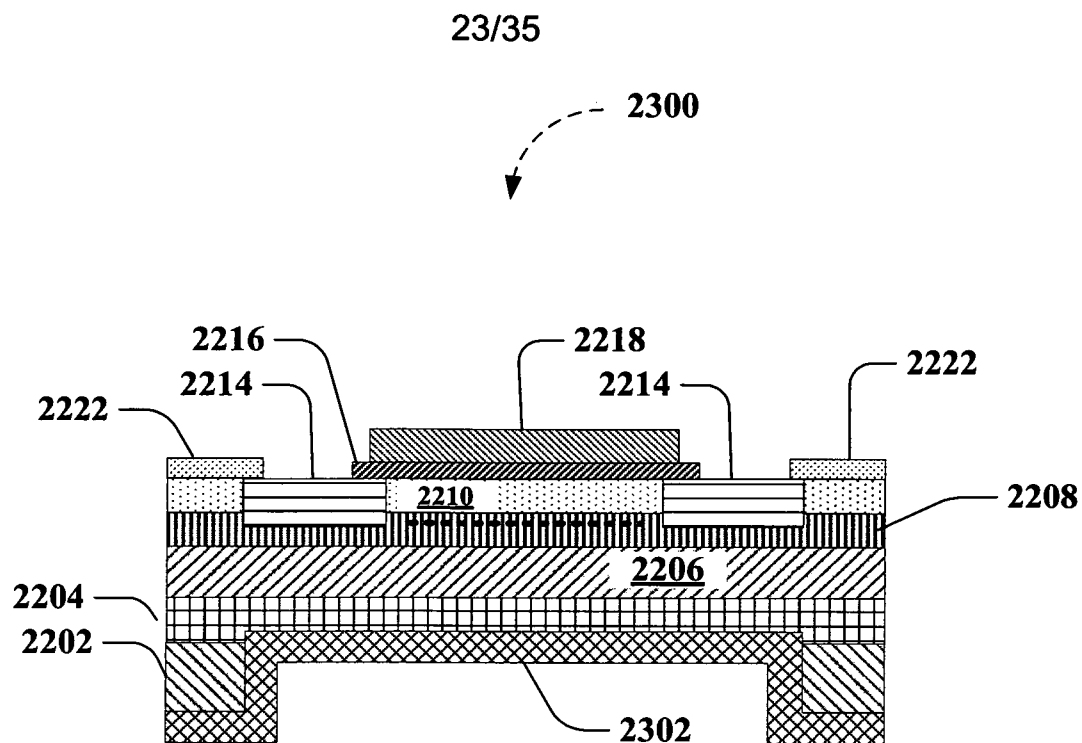


FIG. 22



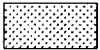
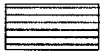
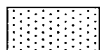
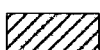
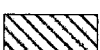
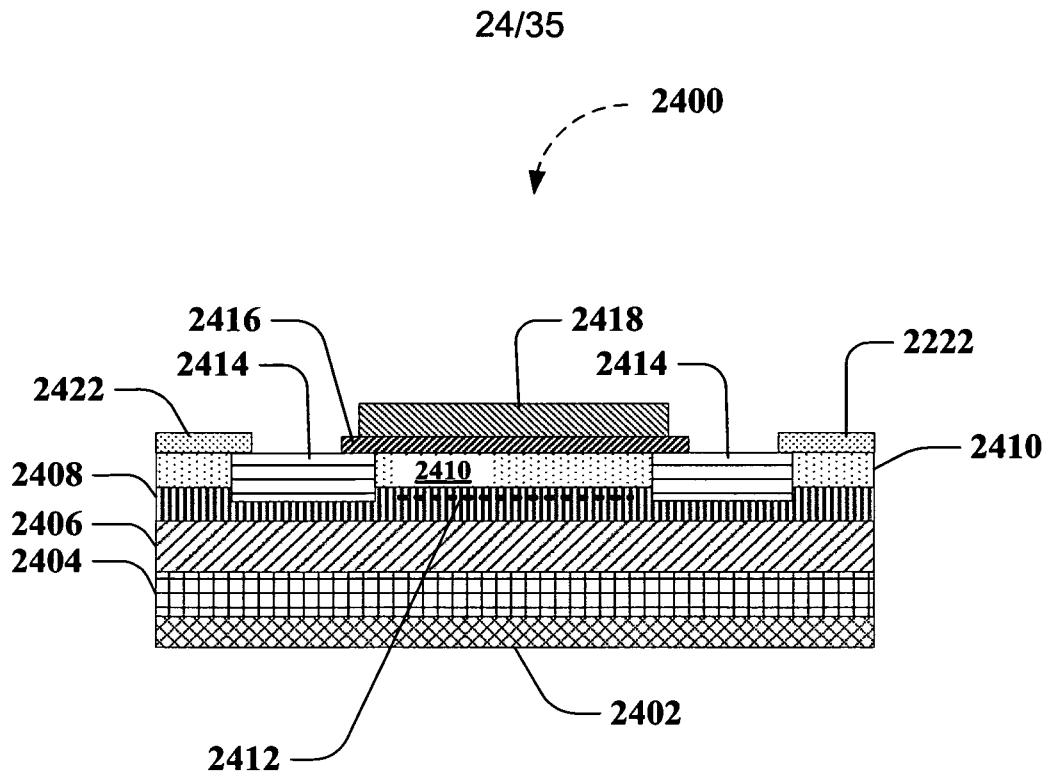
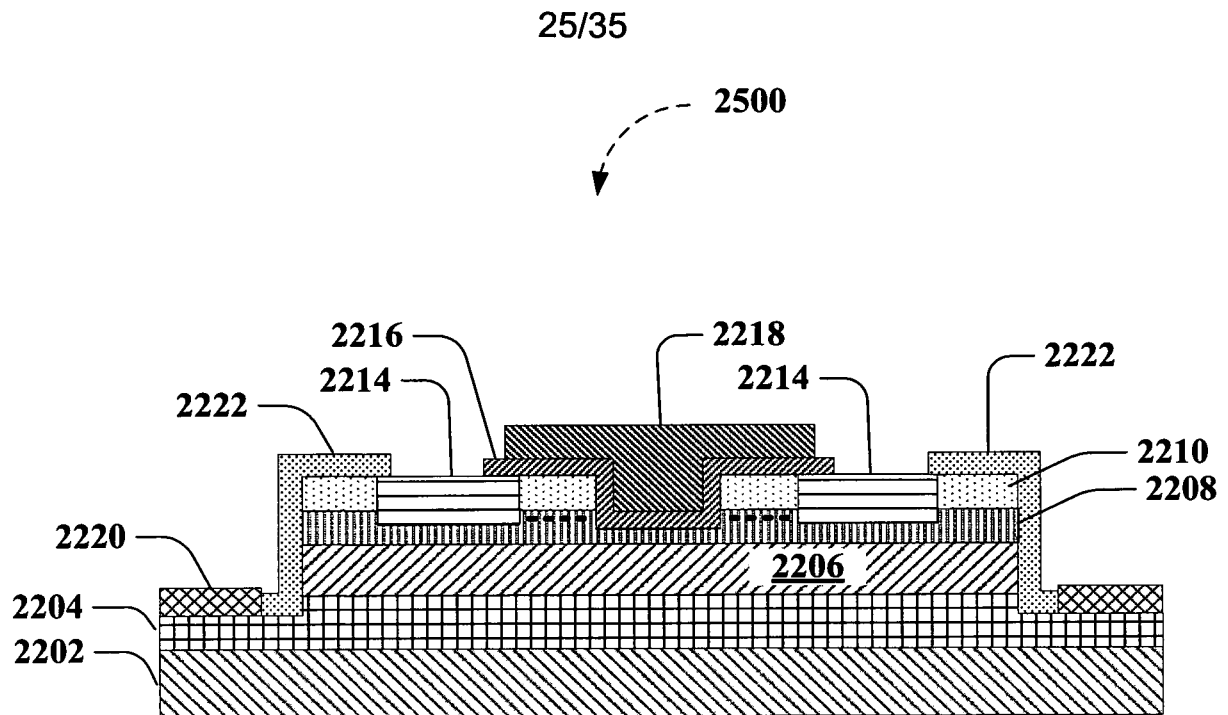
- | | |
|---|-------------------------------------|
|  | Passivation Layer |
|  | Gate Metallization Layer |
|  | Gate Insulating Dielectric Layer |
|  | Source Contact |
|  | Ohmic Drain Contact |
|  | Nitride Semiconductor Barrier Layer |
|  | Second Nitride Semiconductor Layer |
|  | First Nitride Semiconductor Layer |
|  | III-Nitride Material Layer |
|  | Substrate |

FIG. 23



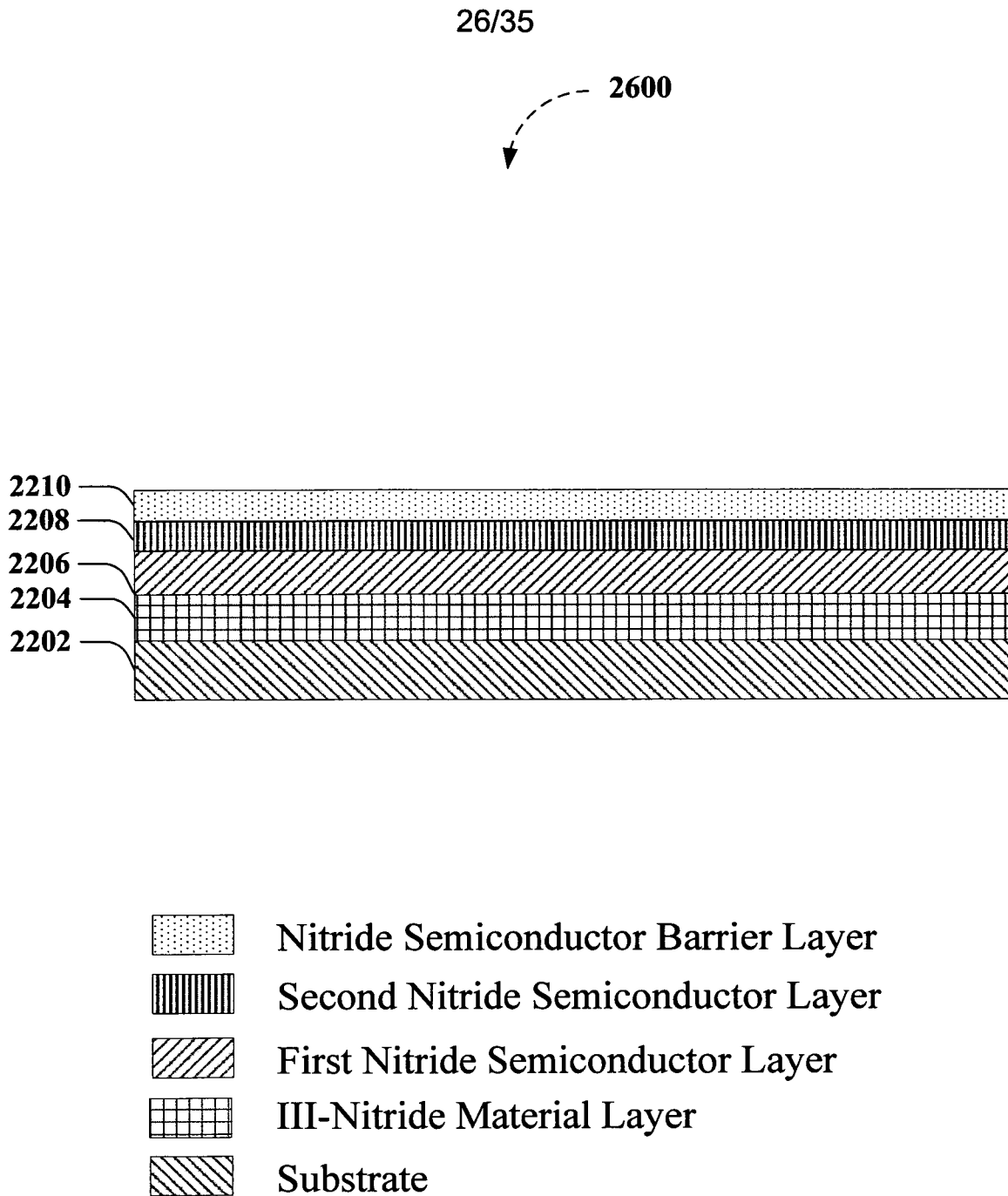
	Passivation Layer
	Gate Metallization Layer
	Gate Insulating Dielectric Layer
	Source Contact
	Ohmic Drain Contact
	Nitride Semiconductor Barrier Layer
	Second Nitride Semiconductor Layer
	First Nitride Semiconductor Layer
	III-nitride Material Substrate Layer

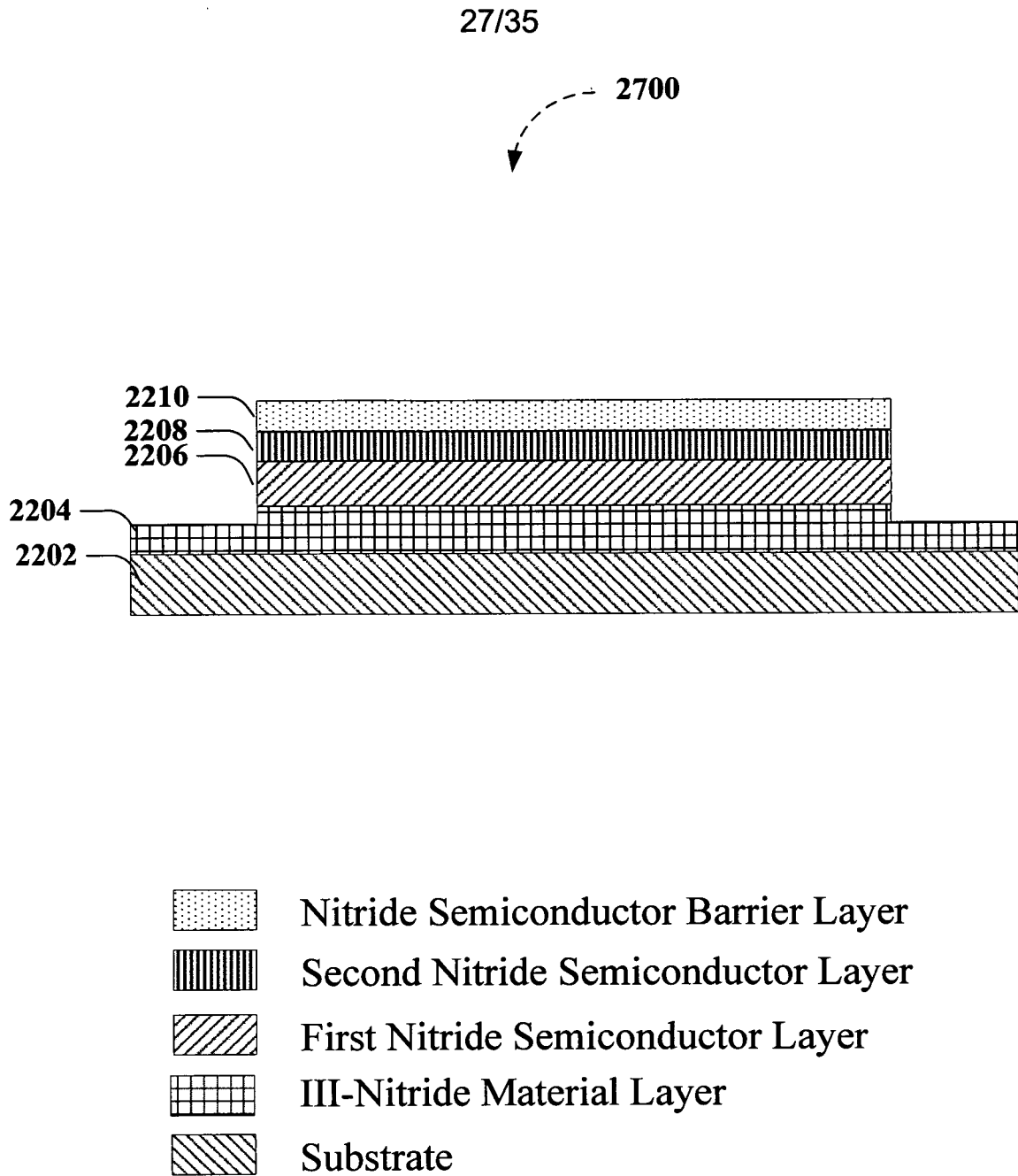
FIG. 24

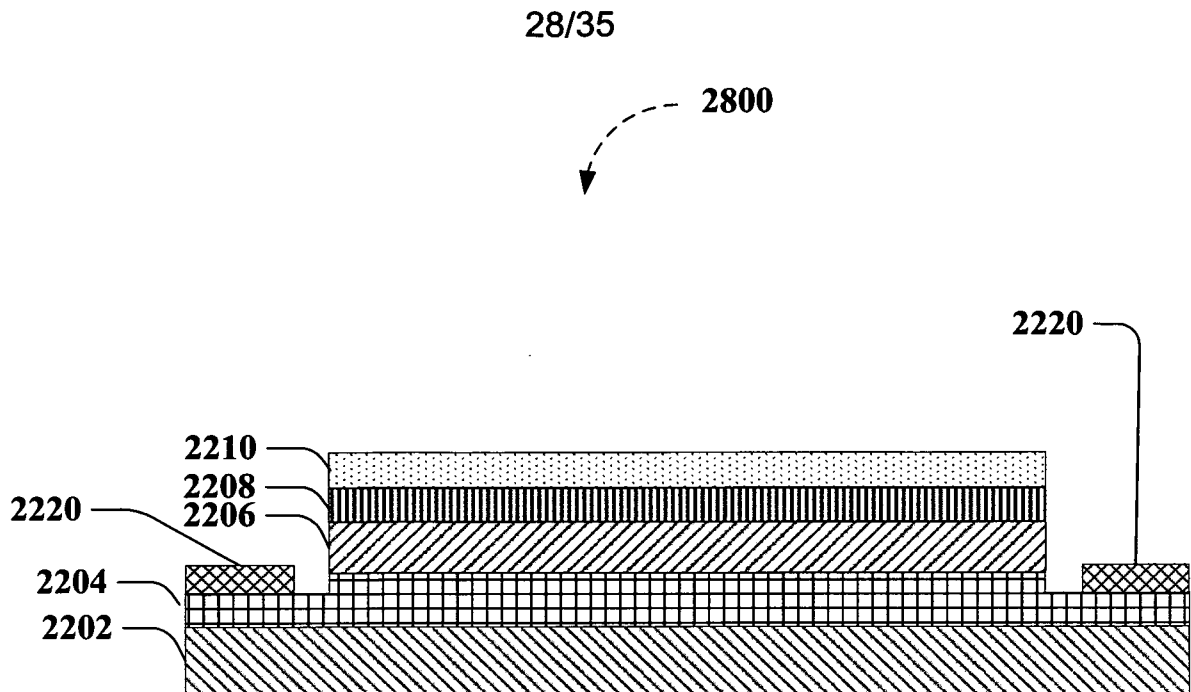


- | | |
|---|-------------------------------------|
|  | Passivation Layer |
|  | Gate Metallization Layer |
|  | Gate Insulating Dielectric Layer |
|  | Source Contact |
|  | Ohmic Drain Contact |
|  | Nitride Semiconductor Barrier Layer |
|  | Second Nitride Semiconductor Layer |
|  | First Nitride Semiconductor Layer |
|  | III-Nitride Material Layer |
|  | Substrate |

FIG. 25

**FIG. 26**

**FIG. 27**



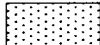
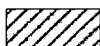
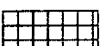
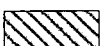
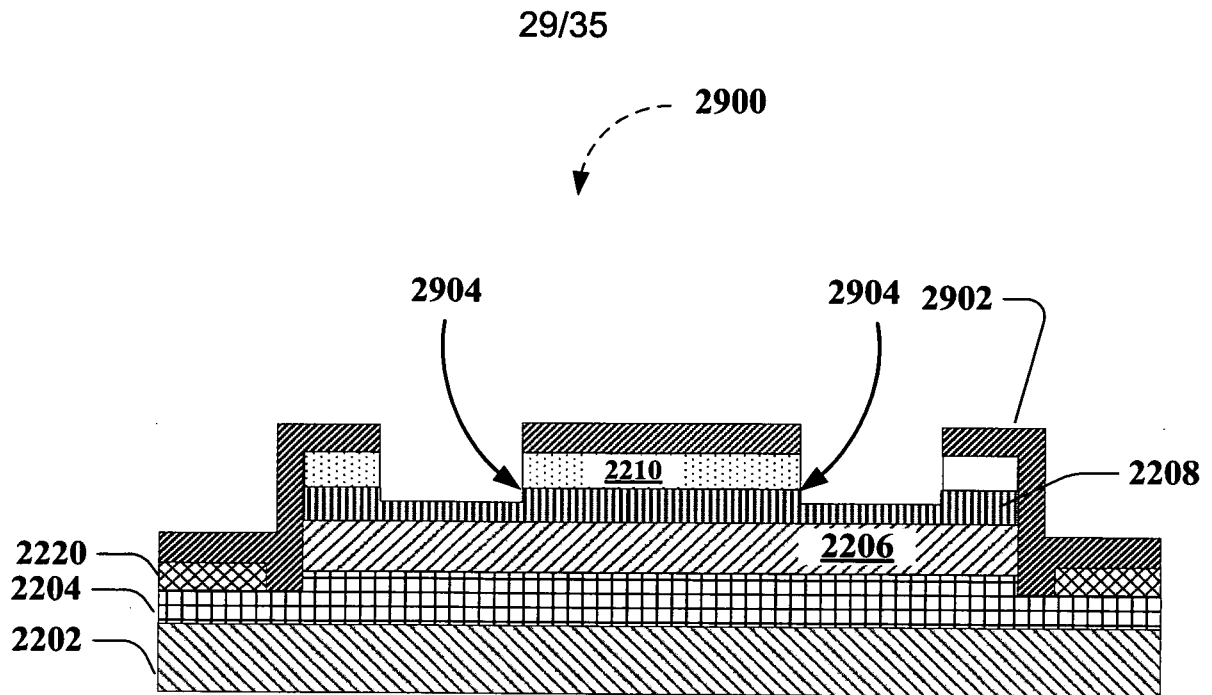
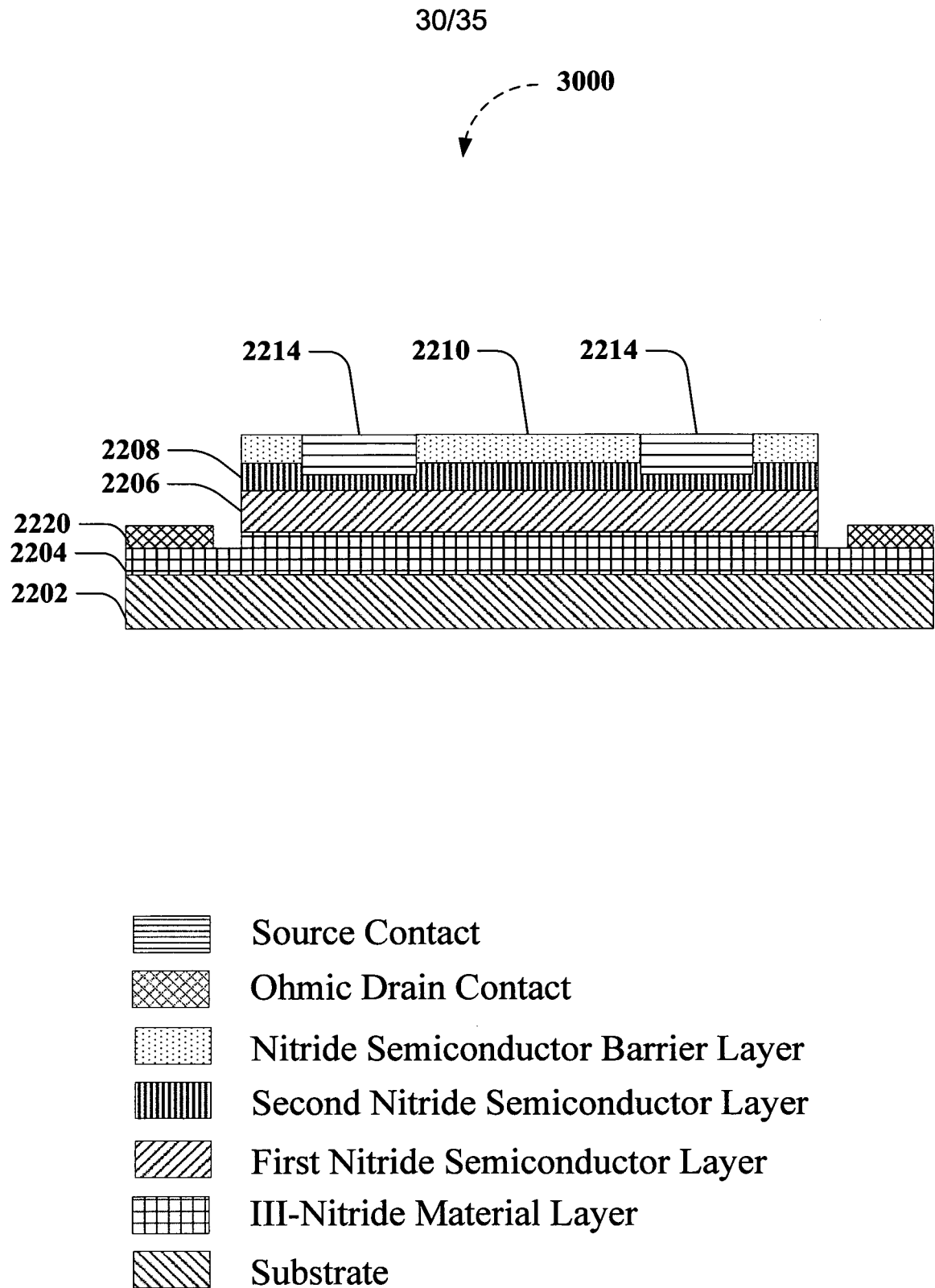
- | | |
|---|-------------------------------------|
|  | Ohmic Drain Contact |
|  | Nitride Semiconductor Barrier Layer |
|  | Second Nitride Semiconductor Layer |
|  | First Nitride Semiconductor Layer |
|  | III-Nitride Material Layer |
|  | Substrate |

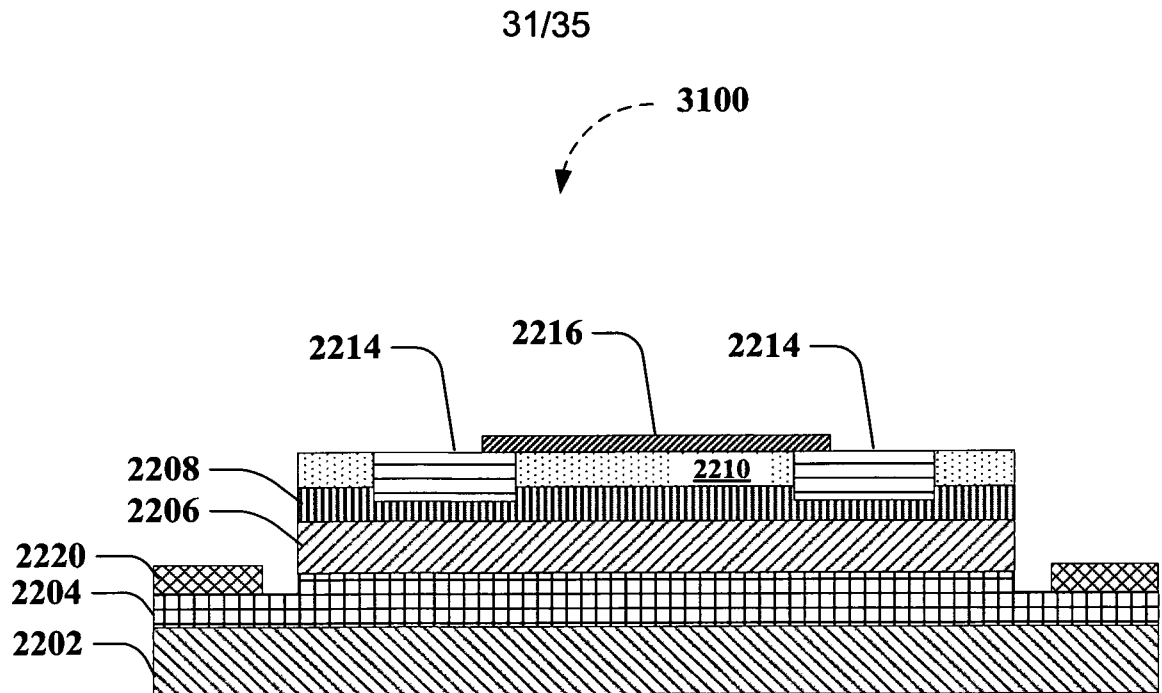
FIG. 28



- | | |
|--|-------------------------------------|
| | Photo Resist Layer |
| | Ohmic Drain Contact |
| | Nitride Semiconductor Barrier Layer |
| | Second Nitride Semiconductor Layer |
| | First Nitride Semiconductor Layer |
| | III-Nitride Material Layer |
| | Substrate |

FIG. 29

**FIG. 30**



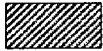
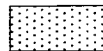
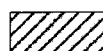
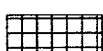
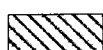
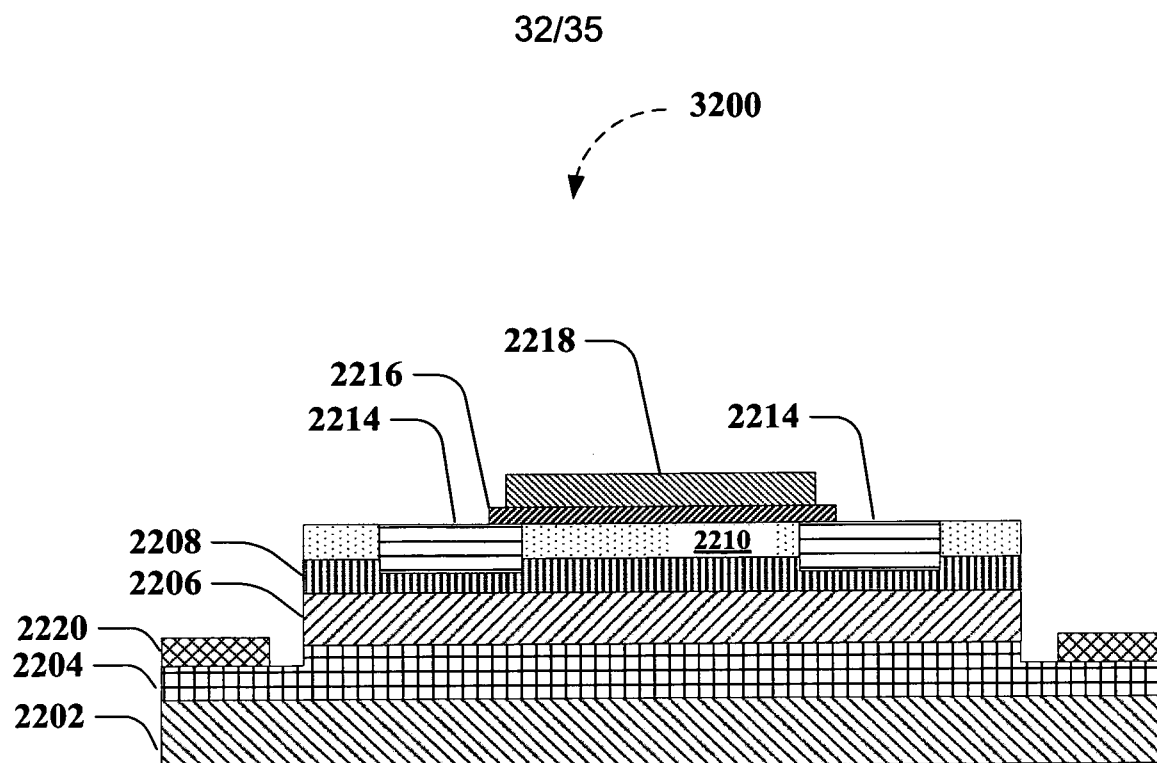
- | | |
|---|-------------------------------------|
|  | Gate Insulating Dielectric Layer |
|  | Source Contact |
|  | Ohmic Drain Contact |
|  | Nitride Semiconductor Barrier Layer |
|  | Second Nitride Semiconductor Layer |
|  | First Nitride Semiconductor Layer |
|  | III-Nitride Material Layer |
|  | Substrate |

FIG. 31



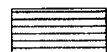
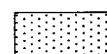
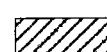
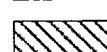
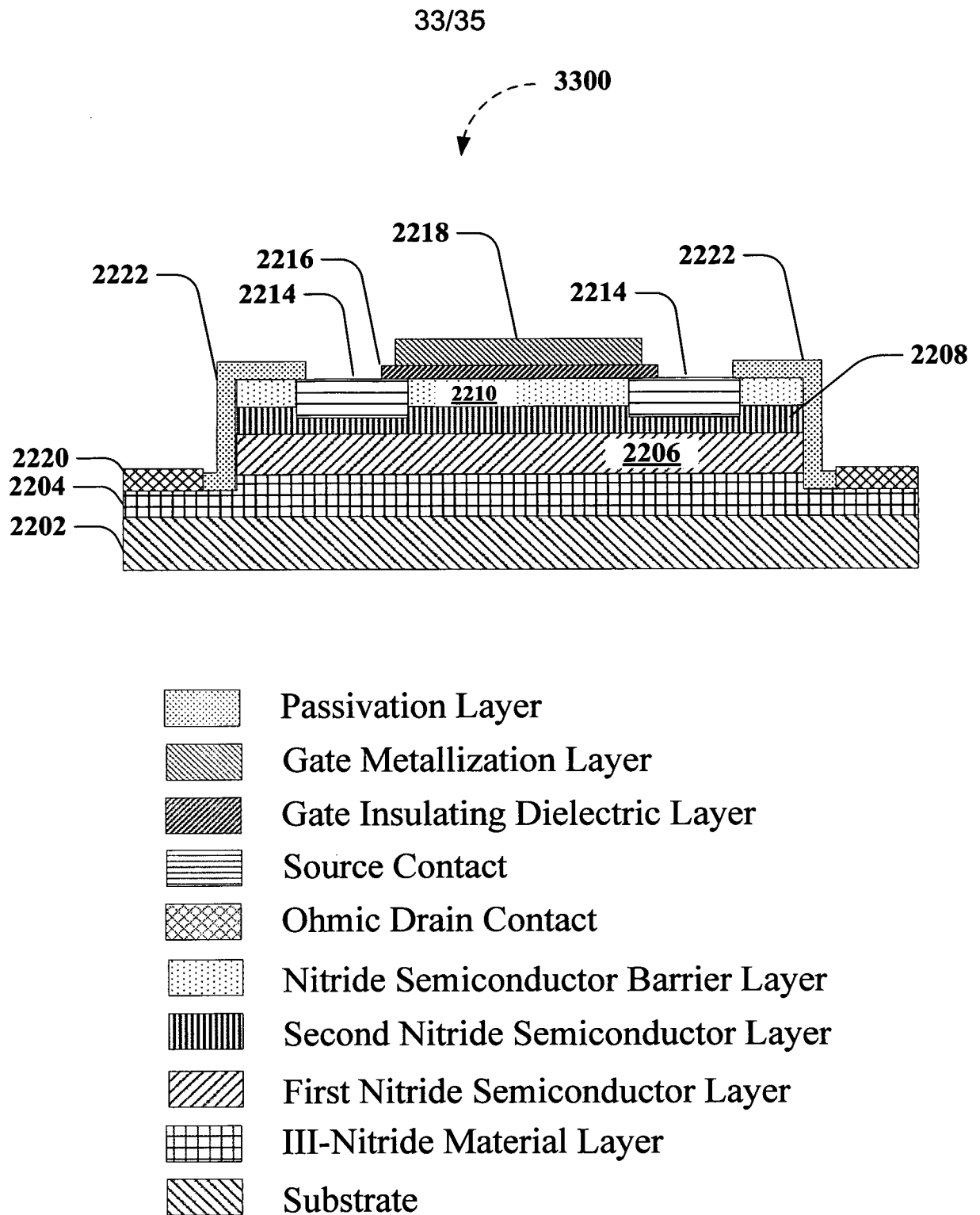
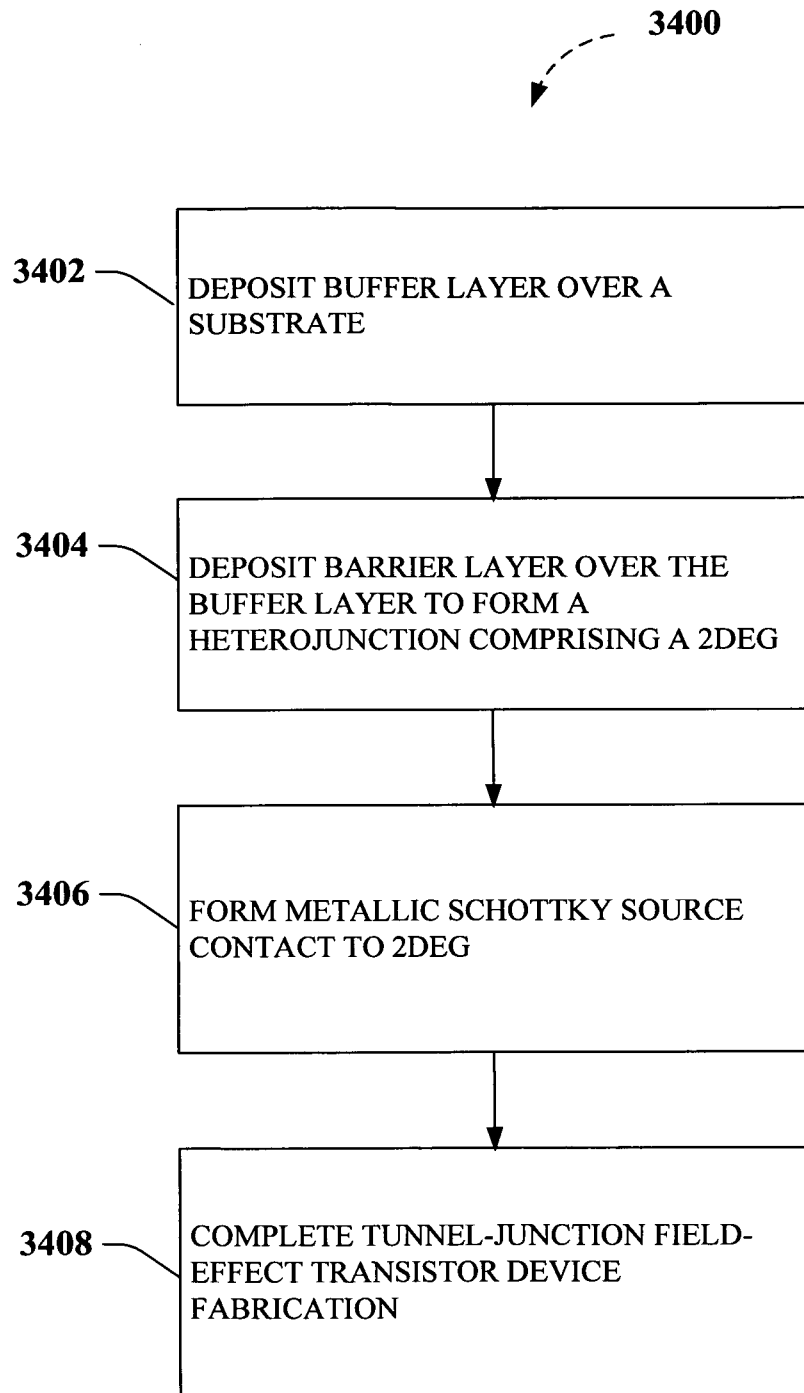
- | | |
|---|-------------------------------------|
|  | Gate Metallization Layer |
|  | Gate Insulating Dielectric Layer |
|  | Source Contact |
|  | Ohmic Drain Contact |
|  | Nitride Semiconductor Barrier Layer |
|  | Second Nitride Semiconductor Layer |
|  | First Nitride Semiconductor Layer |
|  | III-Nitride Material Layer |
|  | Substrate |

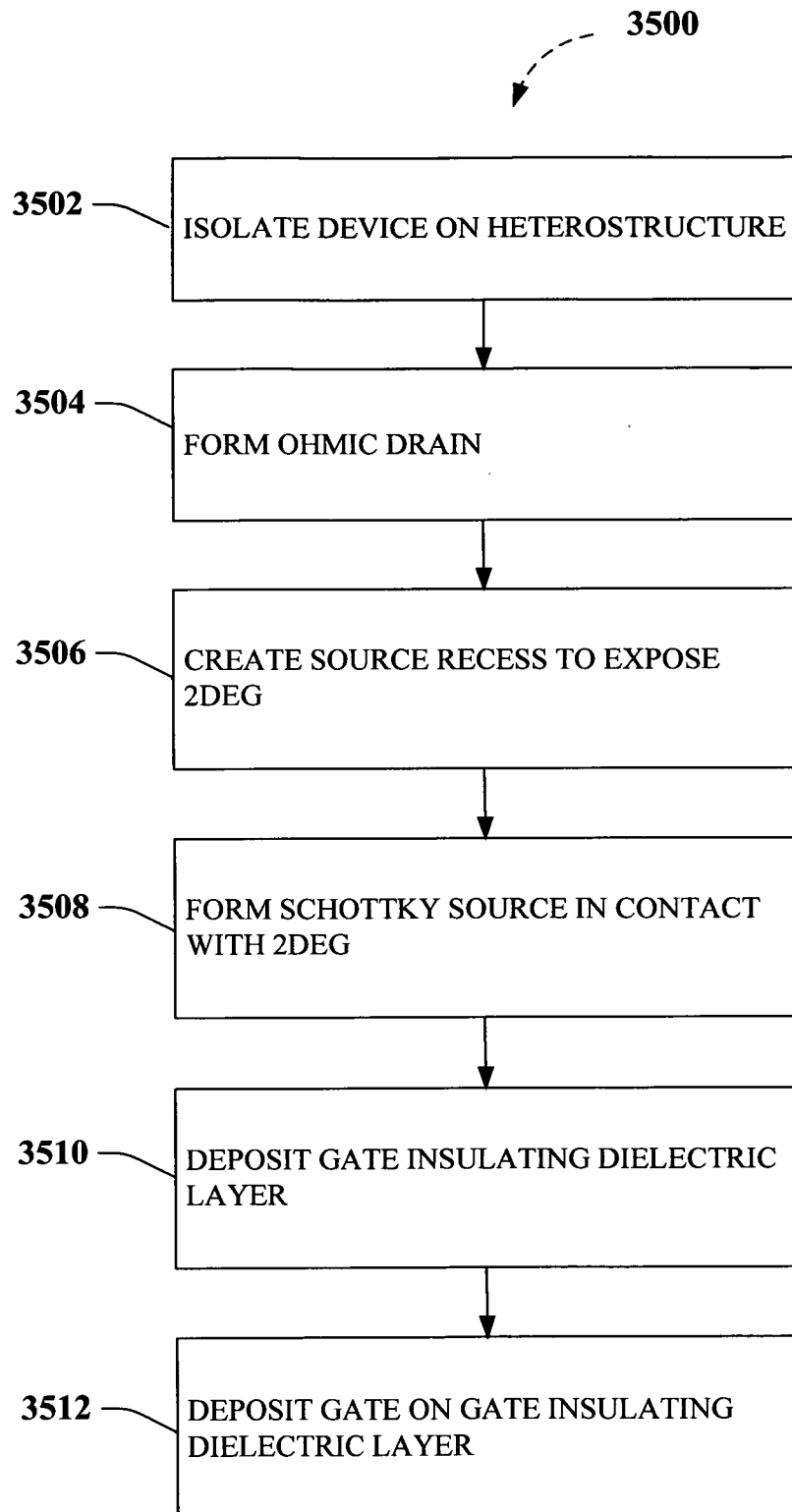
FIG. 32

**FIG. 33**

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**FIG. 34**

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**FIG. 35**

INTERNATIONAL SEARCH REPORT

International application No.

PCT/CN2010/001373

A. CLASSIFICATION OF SUBJECT MATTER

H01L29/778(2006.01)i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC: H01L29/-

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CNPAT,CNKI, WPI, EPODOC: 2DEG, HEMT, HFET, MODFET,TJ-FET,HETERO JUNCTION,SUBSTRATE,SOURCE,NORMALLY OFF,OHMIC CONTACT, SCHOTTKY CONTACT.

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US2009/0146185A1(TRANSPHORM INC.)11 Jun. 2009(11.06.2009) paragraphs [0047]-[0057], fig.3-fig.13	1-6,9-17,19-20
A	CN101320750A(XIAN NENGXUN MICROELECTRONICS CO., LTD.)10 Dec. 2008(10.12.2008) the whole document	1-20
A	CN101604704A(ZHANG, Naiqian)16 Dec. 2009(16.12.2009) the whole document	1-20
A	CN1557024A(CREE INC.)22 Dec. 2004(22.12.2004) the whole document	1-20
A	CN1937206A(NO 55 INST CHINESE ELECTRONIC SCI & TEC)28 Mar. 2007(28.03.2007) the whole document	1-20

☒ Further documents are listed in the continuation of Box C.

☒ See patent family annex.

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"E" earlier application or patent but published on or after the international filing date	"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"L" document which may throw doubts on priority claim (S) or which is cited to establish the publication date of another citation or other special reason (as specified)	"&"document member of the same patent family
"O" document referring to an oral disclosure, use, exhibition or other means	
"P" document published prior to the international filing date but later than the priority date claimed	

Date of the actual completion of the international search 07 Mar. 2011(07.03.2011)	Date of mailing of the international search report 14 Apr. 2011 (14.04.2011)
Name and mailing address of the ISA/CN The State Intellectual Property Office, the P.R.China 6 Xitucheng Rd., Jimen Bridge, Haidian District, Beijing, China 100088 Facsimile No. 86-10-62019451	Authorized officer GUO,Qiang Telephone No. (86-10)62412924

INTERNATIONAL SEARCH REPORT

International application No.
PCT/CN2010/001373

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	CN1 354528A(INST SEMICONDUCTORS CHINESE ACAD SCI)19 Jun. 2002(19.06.2002) the whole document	1-20
A	CN1428870A(KOREA ELECTRONICS&TELECOM RES INST)09 Jul. 2003(09.07.2003) the whole document	1-20

INTERNATIONAL SEARCH REPORT
Information on patent family members

International application No.
PCT/CN2010/001373

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